

256Mb (16M x 16 bit) U t RAM

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K1B5616B2M

Document Title

16Mx16 bit Synchronous Burst Uni-Transistor Random Access Memory

Revision History

<u>Revision No.</u>	<u>History</u>	<u>Draft Date</u>	<u>Remark</u>
0.0	Initial - Design target	July 29, 2005	Preliminary
0.1	Revised - Changed all coordinates in BOND PAD LOCATION AND IDENTIFICATION. - Changed SAMSUNG Logo Location in BONDING INSTRUCTION. - Added 'Mode2 to Mode3' comment in MRS CODE. - Added \overline{ADV} interrupt comment in Burst READ(\overline{ADV} Interrupt) and Burst WRITE(\overline{ADV} Interrupt) - Added 'MRS Option' pad ; floating - 'PS pin MRS & Software MRS' type. connected to Vss - 'Software MRS only' type. - Errata Correction.	September 1, 2005	Preliminary
0.2	Revised - Deleted t_{ADV} , $t_{AS(A)}$, $t_{AH(A)}$, $t_{CSS(A)}$ in Mode 1(Async. Read and Async. Write) - Changed $t_{AS(A)}$ from 0ns to 5ns in Mode 2(Sync. Read and Async. Write)	September 16, 2005	Preliminary
0.21	Revised - Errata Correction in AC test conditions.	November 8, 2005	Preliminary
0.3	Revised - Changed AC Parameter t_{WL} : 10ns \rightarrow 12ns t_{WH} : 10ns(66MHz)/ 8ns(80MHz) \rightarrow 11ns(66MHz)/ 9ns(80MHz) t_{CD} : 10ns(66MHz)/ 8ns(80MHz) \rightarrow 11ns(66MHz)/ 9ns(80MHz) t_{HZ} : 8ns \rightarrow 10ns - Updated Capacitance Value C_{IN} : 8pF C_{IO} : 8pF - Updated DC Parameter ICC2 : 35mA ICC2P : 20mA ICC3 : 35mA ISB1 : 350 μ A(85°C), 200 μ A(40°C) ISBP(1/2) : 250 μ A(85°C), 180 μ A(40°C) ISBP(1/4) : 220 μ A(85°C), 150 μ A(40°C) ISBD : 10 μ A	January 23, 2006	Preliminary
0.4	Revised - Updated monitor pad - Corrected errata	April 5, 2006	Preliminary
1.0	Revised - Corrected tBC (1.2us \rightarrow 1.7us)	May 29, 2006	Final

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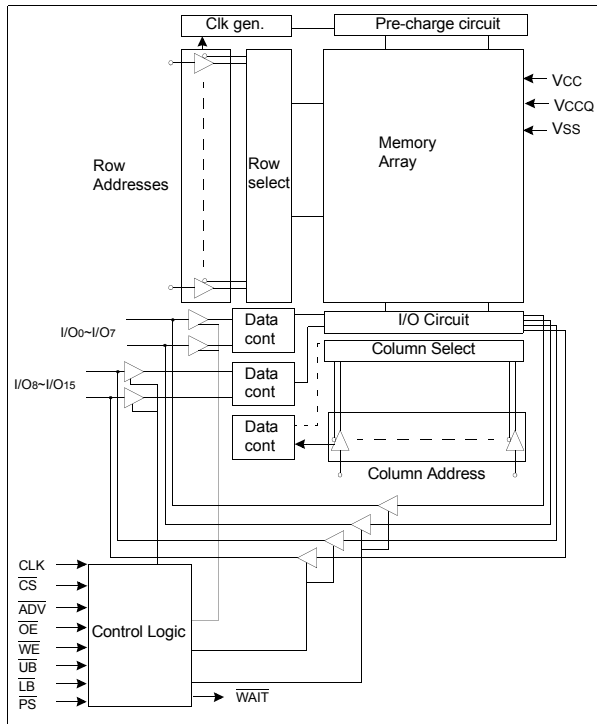
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16M x 16 bit Synchronous Burst Uni-Transistor CMOS RAM

FEATURES & FUNCTION BLOCK DIAGRAM

- Process technology: CMOS
- Organization: 16M x 16 bit
- Power supply voltage: 1.7V~1.95V
- Three state outputs
- Supports MRS (Mode Register Set)
 - PS pin set up
 - Software set up
- Supports power saving modes
 - PAR (Partial Array Refresh)
 - DPD (Deep Power Down)
 - Internal TCSR
- Supports driver strength optimization
- Mode
 - Asynchronous read / Asynchronous write
 - Synchronous burst read / Asynchronous write
 - Synchronous burst read / Synchronous burst write
- Synchronous burst operation
 - Max. clock frequency : 104MHz
 - Fixed and Variable latency
 - 4 / 8 / 16 / 32 and Continuous burst
 - Wrap / No-wrap
 - Latency : 4(Variable) @ 104MHz
 3(Variable) @ 80MHz
 2(Variable) @ 66MHz
- Burst stop
- Burst read suspend
- Burst write data masking



GENERAL PHYSICAL SPECIFICATIONS

- Backside die surface of polished bare silicon
- Typical Die Thickness = 725 μ m
- Typical top-level metallization:
 - Metal: 8K Angstroms thickness Al.
 - 0.2% Si + 0.5% Cu
- Topside Passivation:
 - 6K Angstroms SiN
 - 5 μ m \pm 0.5 μ m Polyimide
- Typical Pad Size: 70 μ m x 100 μ m
- Die Size: 5.978mm x 9.566mm including scribe lane
- Wafer diameter: 8 inch
- Net die/Wafer: 431ea

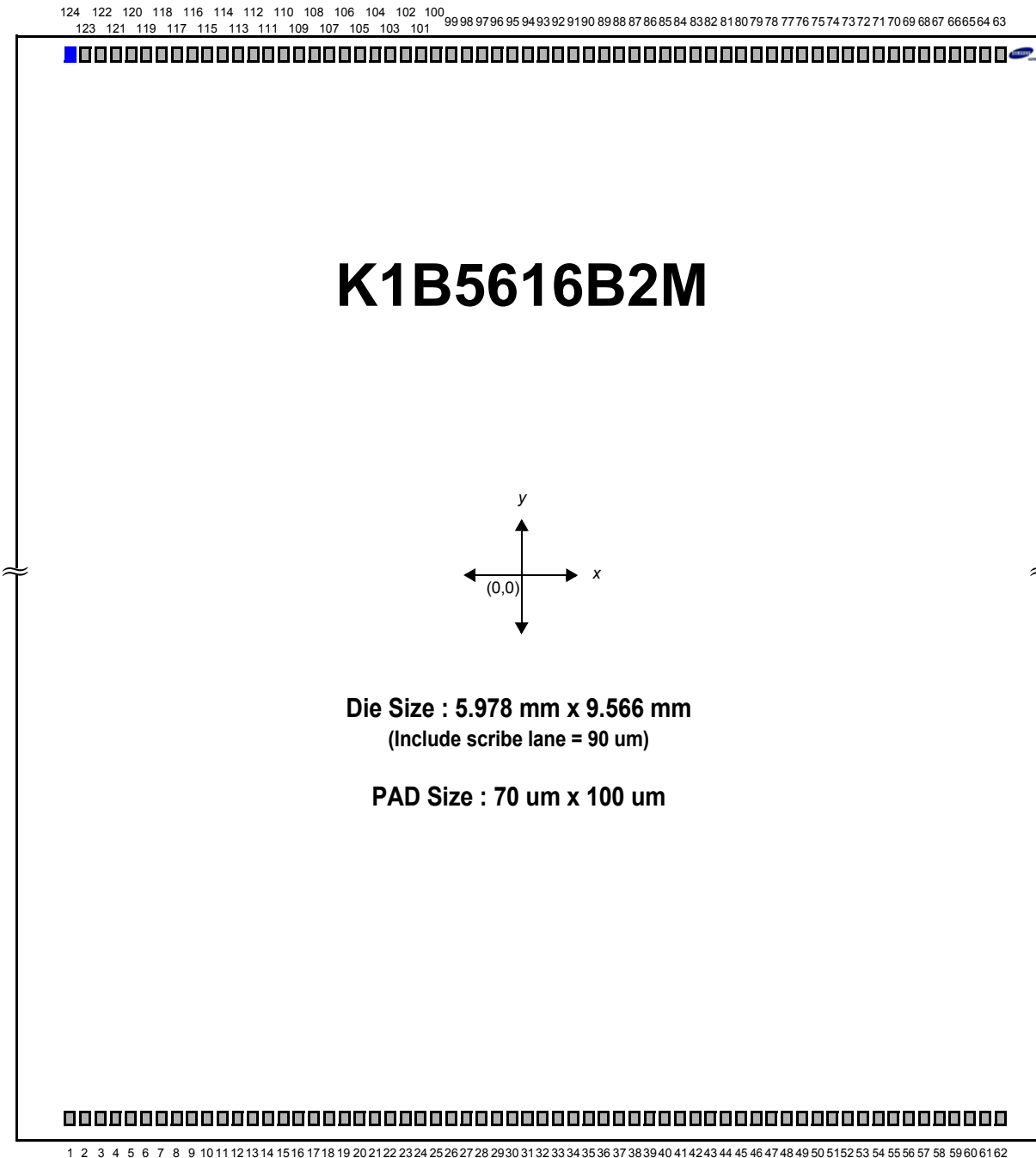
OPTIONS

- K1/W1: DC Probed Die/Wafer @ Hot Temp
- K2/W2: DC/AC Probed Die/Wafer @ Hot Temp
- K3/W3: DC/AC Probed Die/Wafer @ Hot and Cold Temp

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BONDING INSTRUCTIONS

The 256Mb UtRAM M-die has total 124 pads. Refer to the bond pad location and identification table for X, Y coordinates.



* #124 is monitor pad that is needed for Samsung use only, it may looks different color from other pads and should not be bonded.

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BOND PAD LOCATION AND IDENTIFICATION

Unit : mm

PAD#	FUNCTION	X	Y	PAD#	FUNCTION	X	Y
1	DNU	-2.6095	-4.6411	63	DNU	2.6095	4.6411
2	DNU	-2.5240	-4.6411	64	DNU	2.5240	4.6411
3	DNU	-2.4385	-4.6411	65	A16	2.4384	4.6411
4	DNU	-2.3529	-4.6411	66	A15	2.3529	4.6411
5	DNU	-2.2673	-4.6411	67	A14	2.2673	4.6411
6	DNU	-2.1818	-4.6411	68	A13	2.1817	4.6411
7	DNU	-2.0962	-4.6411	69	A12	2.0962	4.6411
8	DNU	-2.0107	-4.6411	70	A11	2.0106	4.6411
9	DNU	-1.9251	-4.6411	71	A10	1.9251	4.6411
10	DNU	-1.8395	-4.6411	72	DNU	1.8395	4.6411
11	IO0	-1.7540	-4.6411	73	DNU	1.7539	4.6411
12	IO8	-1.6684	-4.6411	74	DNU	1.6684	4.6411
13	VCCQ	-1.5829	-4.6411	75	DNU	1.5828	4.6411
14	VSSQ	-1.4973	-4.6411	76	A9	1.4973	4.6411
15	IO1	-1.4117	-4.6411	77	A8	1.4117	4.6411
16	IO9	-1.3262	-4.6411	78	VCC	1.3261	4.6411
17	VCC	-1.2406	-4.6411	79	VCC	1.2406	4.6411
18	VCC	-1.1551	-4.6411	80	VSS	1.1550	4.6411
19	VSS	-1.0695	-4.6411	81	VSS	1.0695	4.6411
20	VSS	-0.9839	-4.6411	82	VSS	0.9839	4.6411
21	DNU	-0.8984	-4.6411	83	A23	0.8983	4.6411
22	IO2	-0.8128	-4.6411	84	A22	0.8128	4.6411
23	IO10	-0.7273	-4.6411	85	A21	0.7272	4.6411
24	VCCQ	-0.6417	-4.6411	86	DNU	0.6417	4.6411
25	VSSQ	-0.5561	-4.6411	87	A20	0.5561	4.6411
26	IO3	-0.4706	-4.6411	88	CLK	0.4705	4.6411
27	IO11	-0.3850	-4.6411	89	WE	0.3850	4.6411
28	OE	-0.2995	-4.6411	90	ADV	0.2994	4.6411
29	DNU	-0.2139	-4.6411	91	PS	0.2139	4.6411
30	DNU	-0.1283	-4.6411	92	DNU	0.1283	4.6411
31	DNU	-0.0428	-4.6411	93	DNU	0.0427	4.6411
32	CLK	0.0428	-4.6411	94	DNU	-0.0427	4.6411
33	DNU	0.1283	-4.6411	95	UB	-0.1283	4.6411
34	DNU	0.2139	-4.6411	96	LB	-0.2139	4.6411
35	DNU	0.2995	-4.6411	97	CS	-0.2994	4.6411
36	IO4	0.3850	-4.6411	98	A19	-0.3850	4.6411
37	IO12	0.4706	-4.6411	99	DNU	-0.4705	4.6411
38	VSSQ	0.5561	-4.6411	100	A18	-0.5561	4.6411
39	VCCQ	0.6417	-4.6411	101	A17	-0.6417	4.6411
40	IO5	0.7273	-4.6411	102	VSS	-0.7272	4.6411
41	IO13	0.8128	-4.6411	103	VSS	-0.8128	4.6411
42	DNU	0.8984	-4.6411	104	VCC	-0.8983	4.6411
43	DNU	0.9839	-4.6411	105	VCC	-0.9839	4.6411
44	DNU	1.0695	-4.6411	106	DNU	-1.0695	4.6411
45	VSS	1.1551	-4.6411	107	A7	-1.1550	4.6411
46	VSS	1.2406	-4.6411	108	DNU	-1.2406	4.6411
47	VCC	1.3262	-4.6411	109	DNU	-1.3261	4.6411
48	VCC	1.4117	-4.6411	110	A6	-1.4117	4.6411
49	IO6	1.4973	-4.6411	111	A5	-1.4973	4.6411
50	IO14	1.5829	-4.6411	112	A4	-1.5828	4.6411
51	VSSQ	1.6684	-4.6411	113	A3	-1.6684	4.6411
52	VCCQ	1.7540	-4.6411	114	MRS Option	-1.7539	4.6411
53	IO7	1.8395	-4.6411	115	VSS	-1.8395	4.6411
54	IO15	1.9251	-4.6411	116	VSS	-1.9251	4.6411
55	WAIT	2.0107	-4.6411	117	A2	-2.0106	4.6411
56	DNU	2.0962	-4.6411	118	DNU	-2.0962	4.6411
57	DNU	2.1818	-4.6411	119	DNU	-2.1817	4.6411
58	DNU	2.2673	-4.6411	120	A1	-2.2673	4.6411
59	DNU	2.3529	-4.6411	121	A0	-2.3529	4.6411
60	DNU	2.4385	-4.6411	122	DNU	-2.4384	4.6411
61	DNU	2.5240	-4.6411	123	DNU	-2.5240	4.6411
62	DNU	2.6096	-4.6411	124	DNU	-2.6095	4.6411

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PAD DESCRIPTION

Name	Function	Type	Description
CLK	Clock	Input	Synchronizes the memory to the system operating frequency during synchronous operations. Commands are referenced to CLK.
$\overline{\text{ADV}}$	Address Valid	Input	Indicates that a valid address is present on the address inputs. Addresses can be latched on the rising edge of $\overline{\text{ADV}}$ during asynchronous READ and WRITE operations.
$\overline{\text{PS}}$	Mode Register set	Input	$\overline{\text{PS}}$ low enables Mode Register to be set and enables either PAR or DPD to be set.
$\overline{\text{CS}}$	Chip Select	Input	$\overline{\text{CS}}$ low enables the chip to be active $\overline{\text{CS}}$ high disables the chip and puts it into standby mode or deep power down mode.
$\overline{\text{OE}}$	Output Enable	Input	Enables the output buffers when LOW. when $\overline{\text{OE}}$ is HIGH, the output buffers are disabled.
$\overline{\text{WE}}$	Write Enable	Input	$\overline{\text{WE}}$ low enables the chip to start writing the data
$\overline{\text{LB}}$	Lower Byte (I/O _{0~7})	Input	$\overline{\text{UB}}$ ($\overline{\text{LB}}$) low enables upper byte (lower byte) to allow data Input/output from I/O buffers.
$\overline{\text{UB}}$	Upper Byte (I/O _{8~15})	Input	
A0~A23	Address 0 ~ Address 23	Input	Inputs for addresses during READ and WRITE operations. Addresses are internally latched during READ and WRITE cycles.
I/O0~I/O15	Data Inputs / Outputs	Input/Output	Depending on $\overline{\text{UB}}$ or $\overline{\text{LB}}$ status, word(16-bit, $\overline{\text{UB}}$ & $\overline{\text{LB}}$ low) data, upper byte(8-bit, $\overline{\text{UB}}$ low & $\overline{\text{LB}}$ high) data or lower byte(8-bit, $\overline{\text{LB}}$ low & $\overline{\text{UB}}$ high) data is loaded
VCC	Voltage Source	Power	Device Power supply. Power supply for device core operation.
VCCQ	I/O Voltage Source	Power	I/O Power supply. Power supply for input/output buffers.
VSS	Ground Source	GND	Ground for device operation
VSSQ	I/O Ground Source	GND	Ground for Input/Output buffers
$\overline{\text{WAIT}}$	Valid Data Indicator	Output	The $\overline{\text{WAIT}}$ signal is output signal indicating the status of the data on the bus whether or not it is valid. $\overline{\text{WAIT}}$ is asserted when a burst crosses a word-line boundary. $\overline{\text{WAIT}}$ is asserted and should be ignored during asynchronous and page mode operations.
DNU	Do Not Use	-	-
MRS Option	MRS input type select	Input	MRS input type select option between ' $\overline{\text{PS}}$ pin & Software' and 'Software only' type. ' $\overline{\text{PS}}$ pin MRS & Software MRS' type is selected when this pad is floating and can not guarantee default modes ¹⁾ . 'Software MRS only' type is selected when this pad is connected to Vss and can guarantee default modes ¹⁾ .

1. Default modes : Asynchronous 4 page Read and Asynchronous Write / DPD disable / PAR disable
Default modes are automatically set after power up or DPD exit.

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FUNCTIONAL SPECIFICATIONS

There are 3 classifications for SAMSUNG die and wafers products, which are K1, K2, and K3 for die and W1, W2 and W3 for wafer, respectively. Each die and wafer support dedicated characteristics and probe the electrical parameters within their specifications. Followings are brief information for die and wafer classifications. Please refer to packaged specifications for more information but these parameters are not guaranteed at bare die and wafer.

• K1 LEVEL DIE OR W1 LEVEL WAFER

The DC parameters are measured by specification for K1 level die or W1 level wafer. The DC parameters measured at 70°C temperature, which called 'Hot DC Sorting'. Other parameters are not guaranteed and warranted including device reliability. Please refer to qualification report for device reliability and package level datasheets for electrical parameters.

• K2 LEVEL DIE OR W2 LEVEL WAFER

The DC parameters and selected AC parameters are measured with for K2 level die or W2 level wafer. The DC characteristics of K2 die and W2 wafer is tested based on DC specifications of K1 level die and W1 level wafer. The DC and specified AC parameters are tested at 70°C temperature, which called 'Hot DC & Selective AC Sorting'. Other parameters are not guaranteed and warranted including device reliability. Please refer to qualification report for device reliability and package level datasheets for electrical parameters.

K2 level die and W2 level wafer probe following AC parameter.

- tRC, tAA, tCO
- tWC, tCW

• K3 LEVEL DIE OR W3 LEVEL WAFER

More selected AC parameters than those of K2 and W2 are tested by specifications. Especially, the cold and hot temperature, -40°C and 85°C is applied while being tested electrical parameters based on K2 level die and W2 level wafer specifications. Other parameters are not guaranteed and warranted including device reliability. Please refer to qualification report for device reliability and package level datasheets for electrical parameters.

K3 level die and W3 level wafer probe following AC parameter.

- tRC, tAA, tCO, tOE
- tWC, tCW, tAS, tAW, tWP, tDW, tDH

PACKING

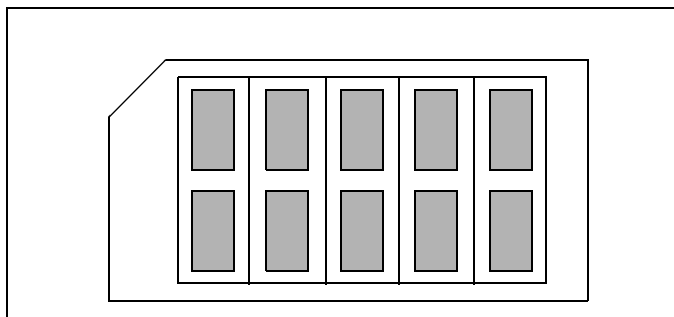
Individual device will be packed in anti-static trays.

• Chip Trays: A 2-inch square waffle style carrier for die with separate compartments for each die. Commonly referred to as a wafer pack, each tray has a cavity size selected for the device that allows for easy loading and unloading and prevents rotation. The tray itself is made of conductive material to reduce the danger of damage to the die from electrostatic discharge.

The chip carriers will be labeled with the following information :

- SAMSUNG wafer lot number
- SAMSUNG part number
- Quantity

• Jar Packing: Jar packing is made by Samsung Electronics and used by many customers that we deliver the requested die as wafer. The pack is consisted of clean paper to wrap the wafer, high cushioned sponge between wafers and hardly fragile plastic box with sponge. Each pack has typically 25 wafers and then several packs are put into larger box depending on amounts of wafers.



Die orientation in chip carriers

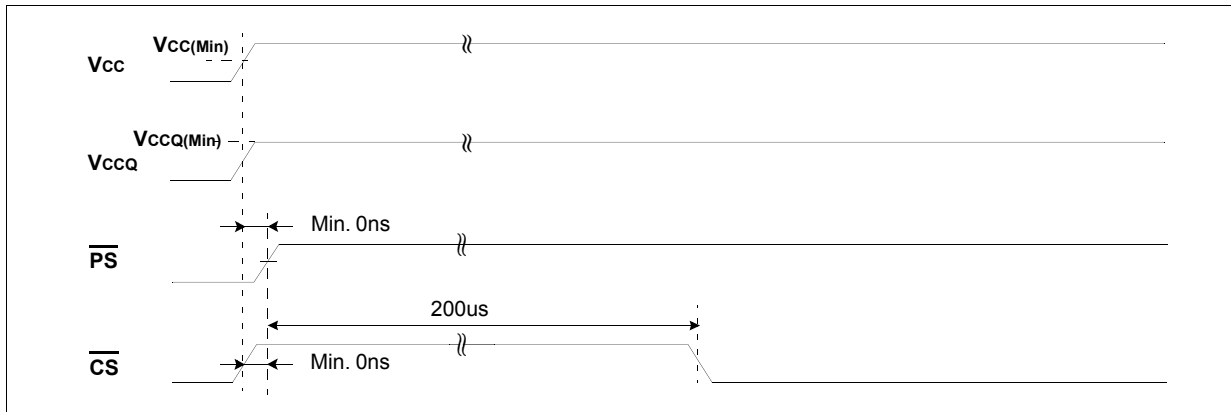
STORAGE AND HANDLING

SAMSUNG recommends the die stored in a controlled environment with filtered nitrogen. The carrier must be opened at ESD safe environment when inspection and assembly.

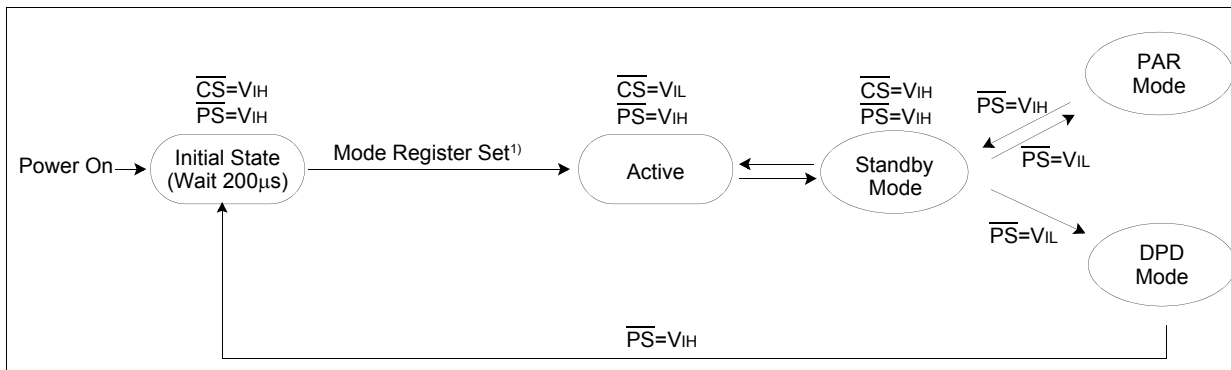
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POWER UP SEQUENCE

After V_{CC} and V_{CCQ} reach minimum operating voltage(1.7V), drive \overline{CS} High first and then drive \overline{PS} High. Then the device gets into the Power Up mode. Wait for minimum 200 μ s to get into the normal operation mode. During the Power Up mode, the standby current can not be guaranteed. To get the stable standby current level, at least one cycle of active operation should be implemented regardless of wait time duration. To get the appropriate device operation, be sure to keep the following power up sequence. MODE1(Asynchronous Read / Asynchronous Write) is set up after power up, but this mode is not always guaranteed.



MODE STATE MACHINE



1) Refer to MRS(Mode Register Set).

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ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Ratings	Unit
Voltage on any pin relative to Vss	V _{IN} , V _{OUT}	-0.2 to V _{CCQ} +0.3V	V
Power supply voltage relative to Vss	V _{CC} , V _{CCQ}	-0.2 to 2.5V	V
Power Dissipation	P _D	1.0	W
Storage temperature	T _{STG}	-65 to 150	°C
Operating Temperature	T _A	-40 to 85	°C

1) Stresses greater than "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to be used under recommended operating condition. Exposure to absolute maximum rating conditions longer than 1 second may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

Item	Symbol	Min	Typ	Max	Unit
Power supply voltage(Core)	V _{CC}	1.7	1.8	1.95	V
Power supply voltage(I/O)	V _{CCQ}	1.7	1.8	1.95	V
Ground	V _{SS} , V _{SSQ}	0	0	0	V
Input high voltage	V _{IH}	0.8 x V _{CCQ}	-	V _{CCQ} +0.2 ²⁾	V
Input low voltage	V _{IL}	-0.2 ³⁾	-	0.4	V

1. T_A=-40 to 85°C, otherwise specified.

2. Overshoot: V_{CCQ}+1.0V in case of pulse width ≤20ns. Overshoot is sampled, not 100% tested.

3. Undershoot: -1.0V in case of pulse width ≤20ns. Undershoot is sampled, not 100% tested.

CAPACITANCE (f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C _{IN}	V _{IN} =0V	-	8	pF
Input/Output capacitance	C _{IO}	V _{IO} =0V	-	8	pF

DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions	Min	Typ	Max	Unit		
Input Leakage Current	I _{LI}	V _{IN} =V _{SS} to V _{CCQ}	-1	-	1	μA		
Output Leakage Current	I _{LO}	$\overline{CS}=V_{IH}$, $\overline{PS}=V_{IH}$, $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$, V _{IO} =V _{SS} to V _{CCQ}	-1	-	1	μA		
Average Operating Current(Async)	I _{CC2}	Cycle time=70ns, I _{IO} =0mA ⁴⁾ , 100% duty, $\overline{CS}=V_{IL}$, $\overline{PS}=V_{IH}$, V _{IN} =V _{IL} or V _{IH}	-	-	35	mA		
	I _{CC2P}	Cycle time=t _{RC} +3t _{PC} , I _{IO} =0mA ⁴⁾ , 100% duty, $\overline{CS}=V_{IL}$, $\overline{PS}=V_{IH}$, V _{IN} =V _{IL} or V _{IH}	-	-	20	mA		
Average Operating Current(Sync)	I _{CC3}	Burst Length 4, Latency 5, 80MHz, I _{IO} =0mA ⁴⁾ , Address transition 1 time, $\overline{CS}=V_{IL}$, $\overline{PS}=V_{IH}$, V _{IN} =V _{IL} or V _{IH}	-	-	35	mA		
Output Low Voltage	V _{OL}	I _{OL} =0.1mA	-	-	0.2	V		
Output High Voltage	V _{OH}	I _{OH} =-0.1mA	1.4	-	-	V		
Standby Current(CMOS)	I _{SB1} ¹⁾	$\overline{CS} \geq V_{CCQ}-0.2V$, $\overline{PS} \geq V_{CCQ}-0.2V$, Other inputs=V _{SS} or V _{CCQ} (Toggle is not allowed) ⁵⁾	< 40°C	-	-	200	μA	
			< 85°C	-	-	350	μA	
Partial Refresh Current	I _{SBP} ²⁾	$\overline{PS} \leq 0.2V$, $\overline{CS} \geq V_{CCQ}-0.2V$, Other inputs=V _{SS} or V _{CCQ} (Toggle is not allowed) ⁵⁾	< 40°C	1/2 Block	-	-	180	μA
				1/4 Block	-	-	150	
			< 85°C	1/2 Block	-	-	250	μA
				1/4 Block	-	-	220	
Deep Power Down Current	I _{SD}	$\overline{PS} \leq 0.2V$, $\overline{CS} \geq V_{CCQ}-0.2V$, Other inputs=V _{SS} or	< 85°C	-	-	10	μA	

1. I_{SB1} is measured after 60ms after CS high. CLK should be fixed at high or at Low.

2. Full Array Partial Refresh Current(I_{SBP}) is same as Standby Current(I_{SB1}).

3. Internal TCSR (Temperature Compensated Self Refresh) is used to optimize refresh cycle below 40°C.

4. I_{IO}=0mA; This parameter is specified with the outputs disabled to avoid external loading effects.

5. V_{IN}=0V; all inputs should not be toggle.

6. Clock should not be inserted between ADV low and WE low during Write operation.

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MRS (MODE REGISTER SET)

The mode registers store the values for the various modes to make UtRAM suitable for a various applications through MRS. There are two ways to perform MRS. One is PS pin MRS and the other is Software MRS. The mode registers have lots of fields and each field consists of several options. Refer to the Table below for detailed Mode Register Setting. A19~A23 addresses are "Don't care" in Mode Register Setting.

MRS CODE

MRS code consists of 12 categories and several options in each category. RARS, PARA, PAR and DPD are related to power saving, BL, WC, Latency, Wrap, WP, MS and IL are related to bus operation and DS is related to device output impedance.

Mode Register Setting according to field of function

Address	A18	A17~A16	A15~A14	A13	A12	A11~A9	A8	A7~A5	A4	A3	A2	A1~A0
Function	IL	DS	MS	WP	Wrap	Latency	WC	BL	DPD	PAR	PARA	PARS

Initial Latency		Driver Strength				Mode Select				
A18	IL	A17	A16	DS	A15	A14	MS			
0	Fixed	0	0	Full Drive	0	0	Mode 1(Async. 4 Page Read / Async. Write)			
1	Variable	0	1	1/2 Drive	0	1	Mode 2(Sync. Burst Read / Async. Write)			
		1	0	1/4 Drive	1	0	Mode 3(Sync. Burst Read / Sync. Burst Write)			

WAIT Polarity		Wrap		Latency Count				Wait Configuration		Burst Length			
A13	WP ¹⁾	A12	Wrap	A11	A10	A9	Latency	A8	WC	A7	A6	A5	BL
0	Low Enable	0	Wrap	1	0	0	2	0	One clock prior	0	1	0	4 word
1	High Enable	1	No-Wrap	0	0	0	3	1	At data	0	1	1	8 word
				0	0	1	4			1	0	0	16 word
				0	1	0	5			1	0	1	32 word
				0	1	1	6			1	1	1	Continuous ²⁾
				1	0	1	7						
				1	1	0	8						
				1	1	1	9						

Deep Power Down		Partial Array Refresh		PAR Array		PAR Size		
A4	DPD	A3	PAR	A2	PARA	A1	A0	PARS
0	DPD Enable	0	PAR Enable	0	Bottom Array	0	0	Full Array
1	DPD Disable	1	PAR Disable	1	Top Array	1	0	1/2 Array
						1	1	1/4 Array

[Note]

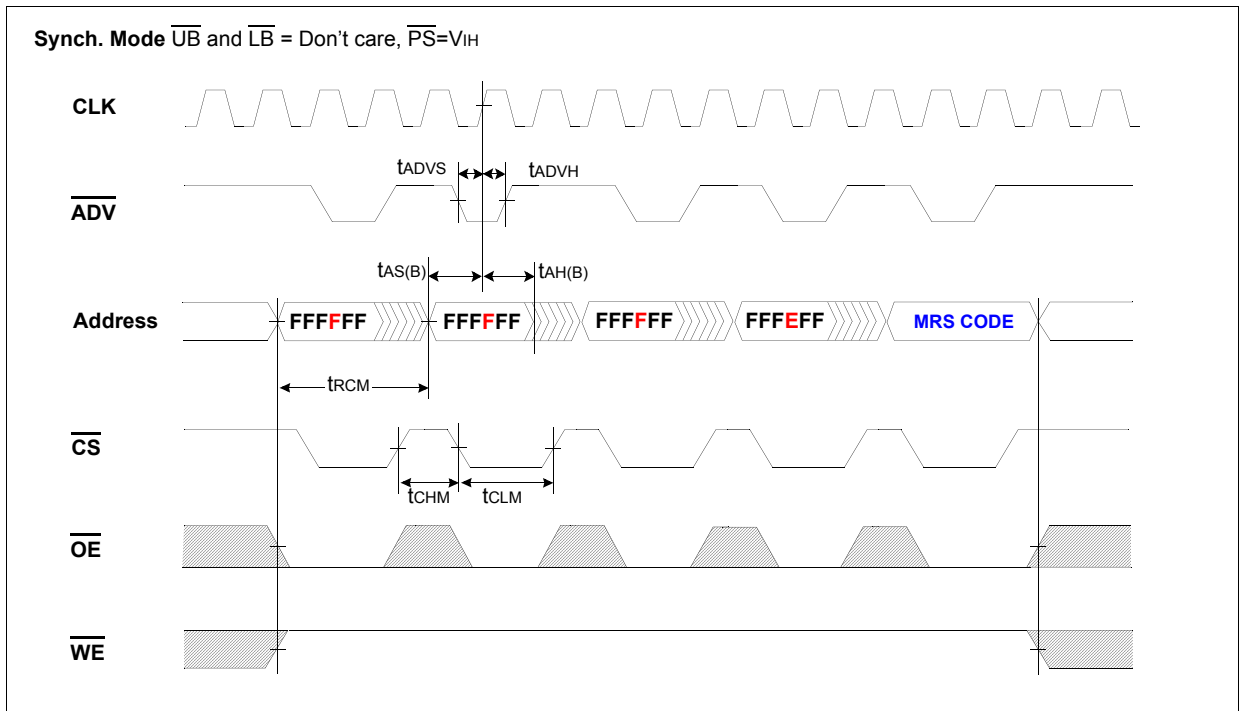
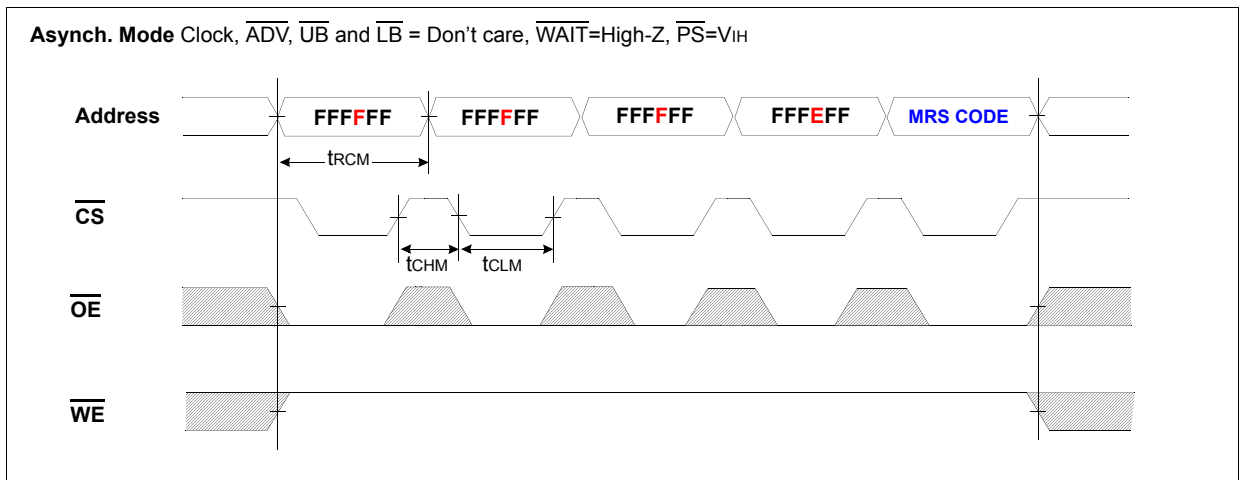
- A19~A23 addresses are "Don't care" & reserved for future use.
- The modes are set automatically to default modes which are 4 Page Read and Asynchronous Write / DPD disable / PAR disable after power up or DPD exit.
- Mode Change Rules.
 - Mode1 to Mode2 (or vice-versa) : No limitation
 - Mode1 to Mode3 : 1 dummy write(to any address with any data) is necessary before setting Mode3
 - * Dummy write: Dummy write timing is just the same with normal write timing. It is necessary because 'Late write' is applied to Asynchronous write as in Mode1.
 - * Late write: The data that is latched in previous write cycle is written in the address that is also latched in previous write cycle when Write starts. And current data and address are latched when Write ends. (WE high or CS high, whichever comes first)
 - Mode3 to Mode1 : 1 dummy write is necessary before setting Mode1
 - * Dummy write: The data and the address should be the same with those which are used during Mode1 to Mode3 transition.

- 1) WP[0]; The data is available when $\overline{\text{WAIT}}$ signal is High. All the timings in this spec are illustrated based on this mode.
WP[1]; The data is available when $\overline{\text{WAIT}}$ signal is Low.
- 2) Refresh command will be denied during continuous operation. $\overline{\text{CS}}$ low should not be longer than tBC(max. 1.7us)

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MRS TIMING WAVEFORM (SOFTWARE)

Software MRS timing consists of 5 Read cycles. Each cycle is normal Read cycle. \overline{CS} pin should be toggling between cycles. 1st, 2nd and 3rd cycle should be FFFFFFFF(h), 4th cycle should be FFFEFF(h) and 5th cycle should be MRS code



Note) Above timing and address condition should not be used in the normal operation. The above condition should be used only for the mode register setting purpose.

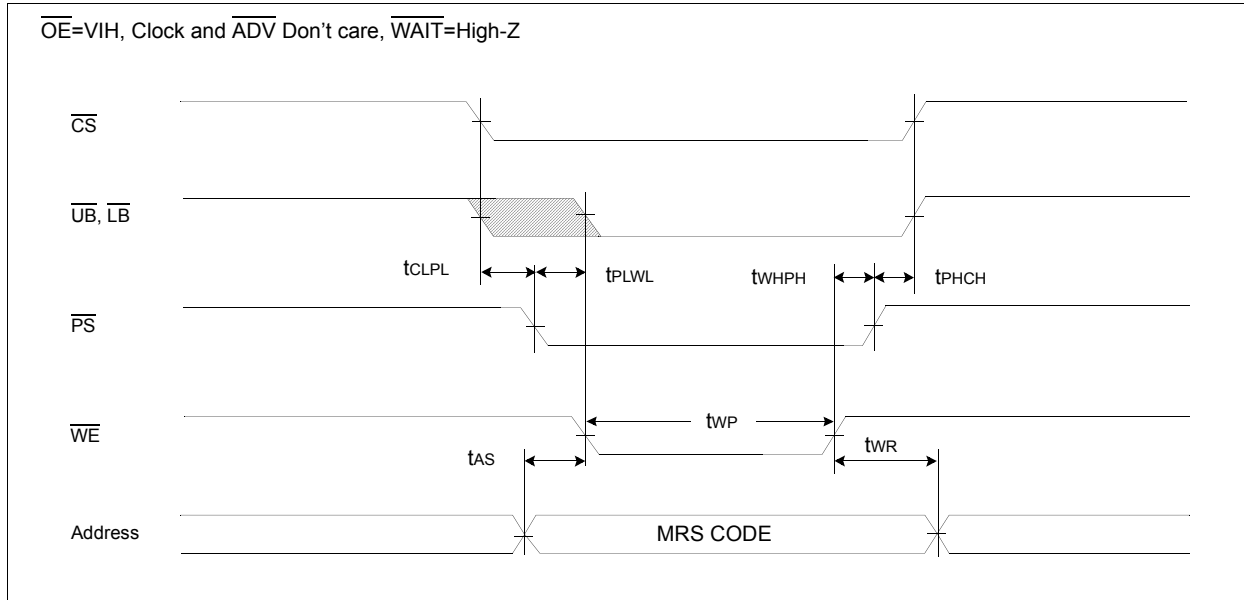
AC CHARACTERISTICS

Parameter List	Symbol	Min	Max	Units	Parameter List	Symbol	Min	Max	Units
\overline{ADV} setup time to clock	t_{ADVS}	3	-	ns	Read cycle time	t_{RCM}	70	-	ns
\overline{ADV} hold time from clock	t_{ADVH}	2	-	ns	\overline{CS} high time	t_{CHM}	10	-	ns
Address setup time to clock	$t_{AS(B)}$	3	-	ns	\overline{CS} low time	t_{CLM}	60	-	ns
Address hold time from clock	$t_{AH(B)}$	2	-	ns					

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MRS TIMING WAVEFORM (\overline{PS} Pin)

MRS can be implemented using by \overline{PS} pin. Serial assertion of control signals of \overline{CS} , \overline{UB} & \overline{LB} , \overline{PS} and \overline{WE} will get the device to be ready for MRS. MRS CODE should be set up before \overline{WE} low and keep the CODE until one of those control signals deserts. MRS terminates when one of those control signals deserts. Clock & \overline{ADV} are don't care in Asynchronous mode.



AC CHARACTERISTICS

	Parameter List	Symbol	Speed		Units
			Min	Max	
MRS	\overline{CS} Low to \overline{PS} Low	t_{CLPL}	0	-	ns
	\overline{PS} Low to \overline{WE} Low	t_{PLWL}	0	-	ns
	\overline{WE} High to \overline{PS} High	t_{WHPH}	0	-	ns
	\overline{PS} High to \overline{CS} High	t_{PHCH}	0	-	ns

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PAR (Partial Array Refresh) mode [A3~A1]

User can select half array, a fourth array as active memory array. The active memory array is periodically refreshed(data stored), whereas the disabled array is not going to be refreshed and so the previously stored data will be invalid. When re-enabling additional portions of the array, the new portions are available immediately upon writing to the MRS.

PAR mode execution;

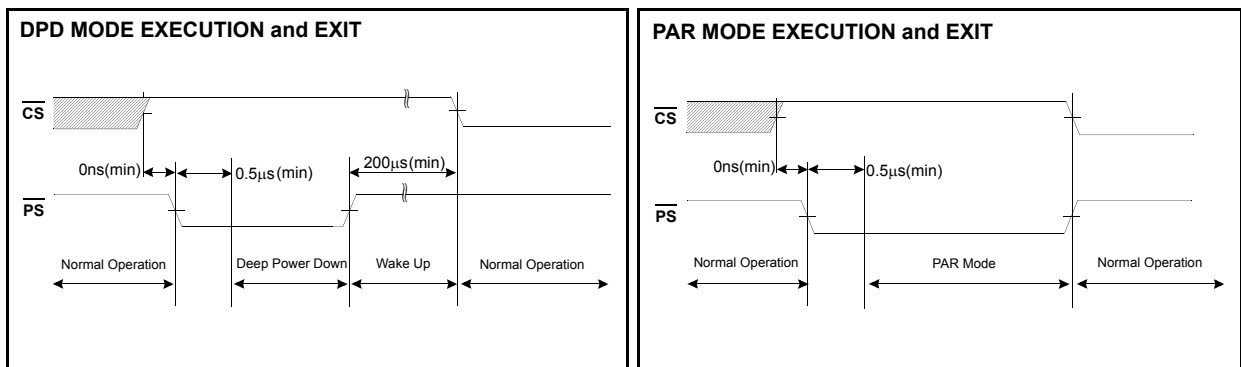
- 1) Mode Register Setting into PAR enable(A3=0)
 DPD enabled setting(A4=0) has higher priority to PAR enabled setting(A3=0). A4=1 is necessary to use PAR mode.
 - 2) PAR mode Enter; keep \overline{PS} signal at V_{IL} for longer than 0.5 μ s during standby mode (Mode Register: A4=1 & A3=0).
 - 3) PAR mode Exit; The device returns to the standby mode when \overline{PS} signal goes to V_{IH} during PAR mode.
- * Mode register values are not changed after the device has been to PAR mode.

DPD (Deep Power Down) mode [A4]

The deep power down mode disables all the refresh related activities. This mode can be used when the system needs to save power. The data become invalid when DPD mode is executed.

DPD mode execution ;

- 1) Mode Register Setting into DPD enable(A4=0)
 - 2) DPD mode Enter; keep \overline{PS} signal at V_{IL} for more than 0.5 μ s during standby mode (Mode Register: A4=0).
 - 3) DPD mode Exit; The device returns to initial State when \overline{PS} signal goes to V_{IH} during DPD mode. Wake up sequence is needed for the device to do normal operation.
- * Mode register values are initialized to default value after the device has been to DPD mode.
 Default modes are 4 Page Read and Asynchronous Write / DPD disable / PAR disable.



STANDBY MODE CHARACTERISTICS

Power Mode	Address (Bottom Array) ²⁾	Address (Top Array) ²⁾	Memory Cell Data	Standby ³⁾ (ISB1, <40°C)	Standby ³⁾ (ISB1, <85°C)	Wait Time(µs)
Standby(Full Array)	000000h ~ FFFFFFFh	000000h ~ FFFFFFFh	Valid ¹⁾	TBD	TBD	0
Partial Refresh(1/2 Block)	000000h ~ 7FFFFFFh	800000h ~ FFFFFFFh	Valid ¹⁾	TBD	TBD	0
Partial Refresh(1/4 Block)	000000h ~ 3FFFFFFh	C00000h ~ FFFFFFFh	Valid ¹⁾	TBD	TBD	0
Deep Power Down	000000h ~ FFFFFFFh		Invalid	TBD	TBD	200

1. Only the data in the selected block are valid
2. PAR Array can be selected through Mode Register Set
3. Standby mode is supposed to be set up after at least one active operation after power up.
 ISB1 is measured after 60ms from the time when standby mode is set up.

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Burst Length [A7~A5] & Wrap [A12]

The device supports 4 word, 8 word, 16 word, 32 word and Continuous burst read or write. and Wrap & No-Wrap are supported for Burst sequence.

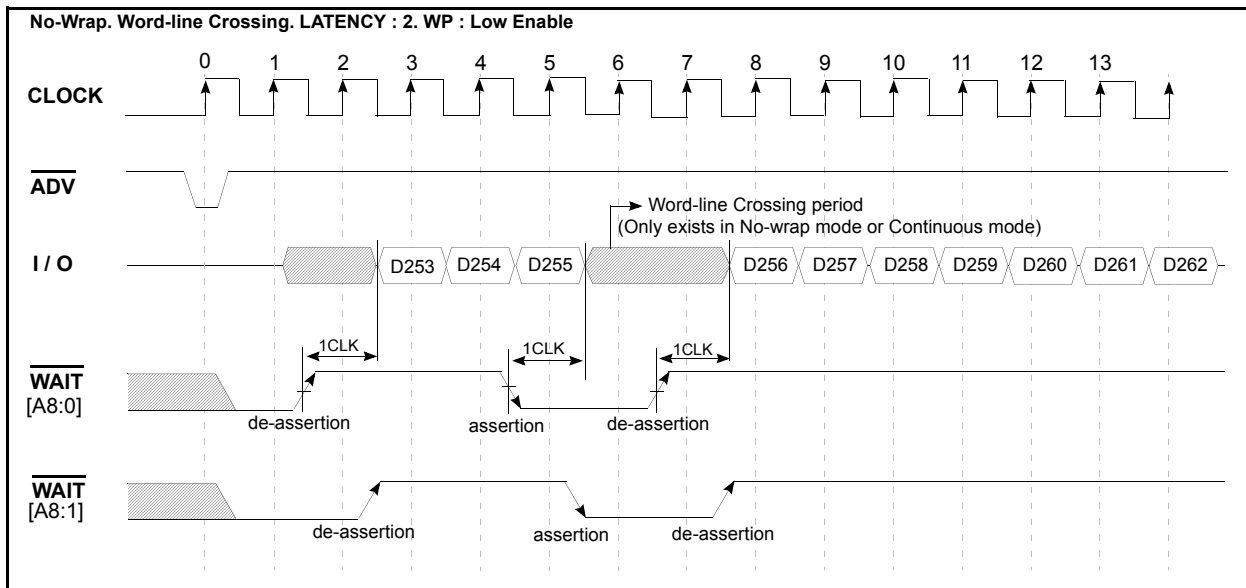
Burst Address Sequence(Decimal)					
Mode	Start	4 word	8 word	16 word	32 word
WRAP	0	0-1-2-3	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-7-8-9-10-11-12-13-14-15	0 - 1 - 2 - 3 - 4 - 5 ~ 26-27-28-29-30-31
	1	1-2-3-0	1-2-3-4-5-6-7-0	1-2-3-4-5-6-7-8-9-10-11-12-13-14-15-0	1 - 2 - 3 - 4 - 5 - 6 ~ 27-28-29-30-31 - 0
	2	2-3-0-1	2-3-4-5-6-7-0-1	2-3-4-5-6-7-8-9-10-11-12-13-14-15-0-1	2 - 3 - 4 - 5 - 6 - 7 ~ 28-29-30-31 - 0 - 1
	3	3-0-1-2	3-4-5-6-7-0-1-2	3-4-5-6-7-8-9-10-11-12-13-14-15-0-1-2	3 - 4 - 5 - 6 - 7 - 8 ~ 29-30-31- 0 - 1 - 2
	~		~	~	~
	7		7-0-1-2-3-4-5-6	7-8-9-10-11-12-13-14-15-0-1-2-3-4-5-6	7 - 8 - 9 - 10 - 11 - 12 ~ 2 - 3 - 4 - 5 - 6
	~		~	~	~
	15			15-0-1-2-3-4-5-6-7-8-9-10-11-12-13-14	15-16-17-18-19-20 ~ 10- 11- 12- 13- 14
~				~	
31				31- 0 - 1 - 2 - 3 - 4 ~ 25-26-27-28-29-30	
No-WRAP	0	0-1-2-3	0- 1- 2- 3- 4- 5- 6- 7	0- 1- 2- 3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15	0 - 1 - 2 - 3 - 4 - 5 ~ 26-27-28-29-30-31
	1	1-2-3-4	1- 2- 3- 4- 5- 6- 7- 8	1- 2- 3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15-16	1 - 2 - 3 - 4 - 5 - 6 ~ 27-28-29-30-31-32
	2	2-3-4-5	2- 3- 4- 5- 6- 7- 8- 9	2- 3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15-16-17	2 - 3 - 4 - 5 - 6 - 7 ~ 28-29-30-31-32-33
	3	3-4-5-6	3- 4- 5- 6- 7- 8- 9-10	3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15-16-17-18	3 - 4 - 5 - 6 - 7 - 8 ~ 29-30-31-32-33-34
	~		~	~	~
	7		7-8-9-10-11-12-13-14	7-8-9-10-11-12-13-14-15-16-17-18-19-20-21-22	7 - 8 - 9 - 10-11-12 ~ 33-34-35-36-37-38
	~		~	~	~
	15			15-16-17-18-19-20-21-22-23-24-25-26-27-28-29-30	15-16-17-18-19-20 ~ 41-42-43-44-45-46
~				~	
31				31-32-33-34-35-36 ~ 57-58-59-60-61-62	

1. Continuous Burst mode needs to meet tBC(max. 1.7us) parameter.

WAIT Configuration [A8] & WAIT Polarity [A13]

The WAIT signal is output signal indicating the status of the data on the bus whether or not it is valid. WAIT configuration is to decide the timing when WAIT asserts or deserts. WAIT asserts (or deserts) one clock prior to the data when A8 is set to 0. (WAIT asserts (or deserts) at data clock when A8 is set to 1). WAIT polarity is to decide the WAIT signal level at which data is valid or invalid. Data is valid if WAIT signal is high when A13 is set to 0. (Data is valid if WAIT signal is low when A13 is set to 1). All the timing diagrams in this SPEC are illustrated based on following setup; [A13 : 0] and [A8 : 0].

Below timing shows WAIT signal's movement when word boundary crossing happens in No-wrap mode.



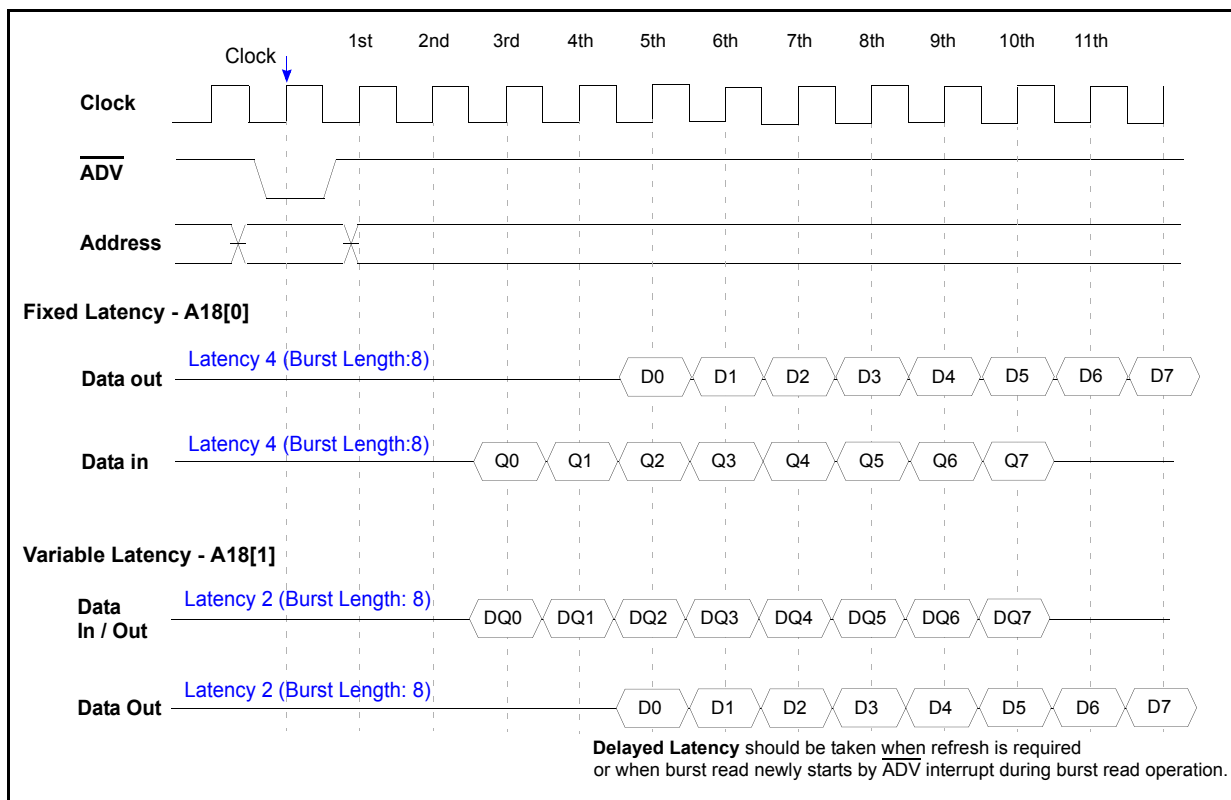
K1B5616B2M

Latency [A11~A9]

The Latency stands for the number of clocks before the first data available from the burst command.

Item	Upto 66MHz		Upto 80MHz		Upto 104MHz	
	Fixed	Variable	Fixed	Variable	Fixed	Variable
Latency Set(A11:A10:A9)	4(0:0:1)	2(1:0:0)	5(0:1:0)	3(0:0:0)	7(1:0:1)	4(0:0:1)
Read Latency(min)	4	2 / 4 ¹⁾	5	3 / 5 ¹⁾	7	4 / 7 ¹⁾
1st Read data fetch clock	5th	3rd / 5th ¹⁾	6th	4th / 6th ¹⁾	8th	5th / 8th ¹⁾
Write Latency(min)	2	2	3	3	4	4
1st Write data loading clock	3rd	3rd	4th	4th	5th	5th

1) Delayed Latency should be taken when refresh is required or when burst read newly starts by ADV interrupt during burst read operation.



Driver Strength [A17~A16]

The optimization of output driver strength is possible to adjust for the different data loadings. The device can minimize the noise generated on the data bus during read operation. The device supports full, 1/2 and 1/4 driver strength. The device's default mode is Full driver strength.

Driver Strength	Full	1 / 2	1 / 4
IMPEDANCE(typ.)	40Ω	90Ω	150Ω

1. Impedance values are typical values, not 100% tested.

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OPERATION MODE [A15~A14]

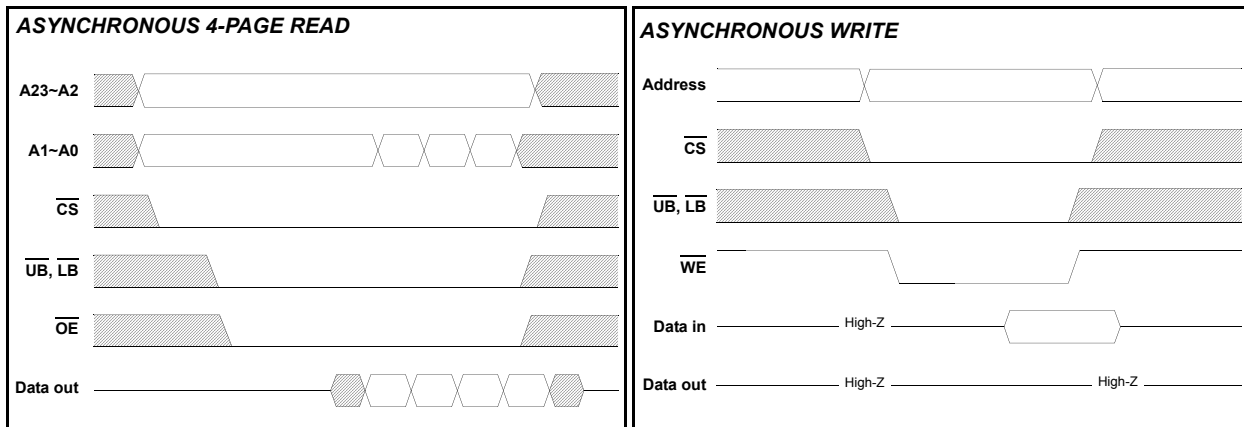
MODE1. ASYNCHRONOUS READ / ASYNCHRONOUS WRITE MODE

Asynchronous read operation

Asynchronous read operation starts when \overline{CS} , \overline{OE} and \overline{UB} or \overline{LB} are asserted. First data come out after random access time(t_{AA}) but second, third and fourth data come out after page access time(t_{PA}) when using the page addresses (A0, A1). \overline{PS} and \overline{WE} should be de-asserted during read operation. Clock, \overline{ADV} are don't care during read operation and \overline{WAIT} is Hi-Z.

Asynchronous write operation

Asynchronous write operation starts when \overline{CS} , \overline{WE} and \overline{UB} or \overline{LB} are asserted. \overline{PS} and should be de-asserted during write operation. Clock, \overline{OE} , \overline{ADV} are don't care during write operation and \overline{WAIT} signal is Hi-Z.



FUNCTIONAL DESCRIPTION

\overline{CS}	\overline{PS}	\overline{OE}	\overline{WE}	\overline{LB}	\overline{UB}	I/O0~7	I/O8~15	Mode	Power
H	H	X ¹⁾	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	High-Z	Deselected	Standby
H	L	X ¹⁾	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	High-Z	Deselected	DPD or PAR
L	H	H	H	X ¹⁾	X ¹⁾	High-Z	High-Z	Output Disabled	Active
L	H	X ¹⁾	X ¹⁾	H	H	High-Z	High-Z	Output Disabled	Active
L	H	L	H	L	H	Dout	High-Z	Lower Byte Read	Active
L	H	L	H	H	L	High-Z	Dout	Upper Byte Read	Active
L	H	L	H	L	L	Dout	Dout	Word Read	Active
L	H	H	L	L	H	Din	High-Z	Lower Byte Write	Active
L	H	H	L	H	L	High-Z	Din	Upper Byte Write	Active
L	H	H	L	L	L	Din	Din	Word Write	Active

1. X means "Don't care". X should be low or high state.
2. In asynchronous mode, Clock and \overline{ADV} are ignored. Clock and \overline{ADV} should be low or high state.
3. \overline{WAIT} pin is High-Z in Asynchronous mode.

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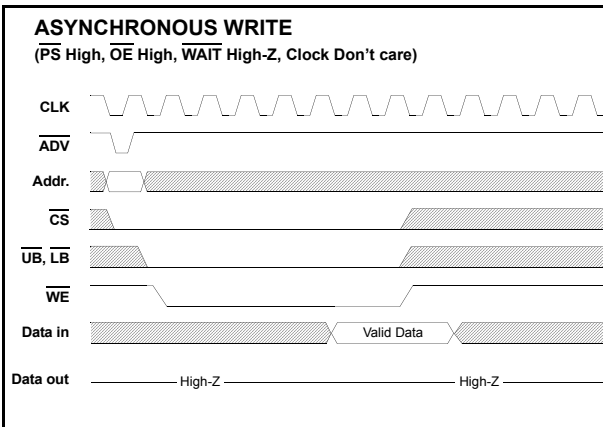
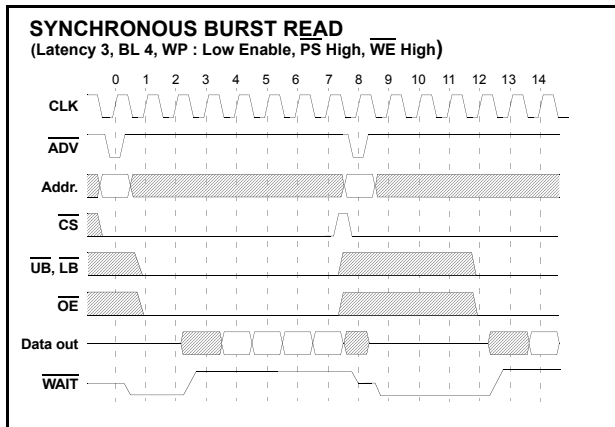
MODE2. SYNCHRONOUS BURST READ / ASYNCHRONOUS WRITE MODE

Synchronous Burst Read Operation

Burst Read command is implemented when \overline{ADV} is detected low at clock rising edge. \overline{WE} should be de-asserted during Burst read, Burst operation re-starts whenever \overline{ADV} is detected low at clock rising edge even in the middle of operation. Variable latency allows the UTRAM to be configured for minimum latency at high frequencies, but the controller must monitor \overline{WAIT} to detect any conflict with refresh cycles.

Asynchronous Write Operation

Asynchronous write operation starts when \overline{CS} , \overline{WE} and \overline{UB} or \overline{LB} are asserted. \overline{PS} and should be de-asserted during write operation. Clock, \overline{OE} , \overline{ADV} are don't care during write operation and \overline{WAIT} signal is Hi-Z.



FUNCTIONAL DESCRIPTION

\overline{CS}	\overline{PS}	\overline{OE}	\overline{WE}	\overline{LB}	\overline{UB}	I/O ₀₋₇	I/O ₈₋₁₅	CLK	\overline{ADV}	Mode	Power
H	H	X ¹⁾	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	High-Z	X ¹⁾	X ¹⁾	Deselected	Standby
H	L	X ¹⁾	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	High-Z	X ¹⁾	X ¹⁾	Deselected	PAR
L	H	H	H	X ¹⁾	X ¹⁾	High-Z	High-Z	X ¹⁾	H	Output Disabled	Active
L	H	X ¹⁾	X ¹⁾	H	H	High-Z	High-Z	X ¹⁾	H	Output Disabled	Active
L	H	X ¹⁾	H	X ¹⁾	X ¹⁾	High-Z	High-Z			Read Command	Active
L	H	L	H	L	H	Dout	High-Z		H	Lower Byte Read	Active
L	H	L	H	H	L	High-Z	Dout		H	Upper Byte Read	Active
L	H	L	H	L	L	Dout	Dout		H	Word Read	Active
L	H	H	L	L	H	Din	High-Z	X ¹⁾		Lower Byte Write	Active
L	H	H	L	H	L	High-Z	Din	X ¹⁾		Upper Byte Write	Active
L	H	H	L	L	L	Din	Din	X ¹⁾		Word Write	Active

1. X means "Don't care". X should be low or high state.

2. \overline{WAIT} is device output signal so does not have any affect to the mode definition. Please refer to each timing diagram for \overline{WAIT} pin function.

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MODE3. SYNCHRONOUS BURST READ / SYNCHRONOUS BURST WRITE MODE

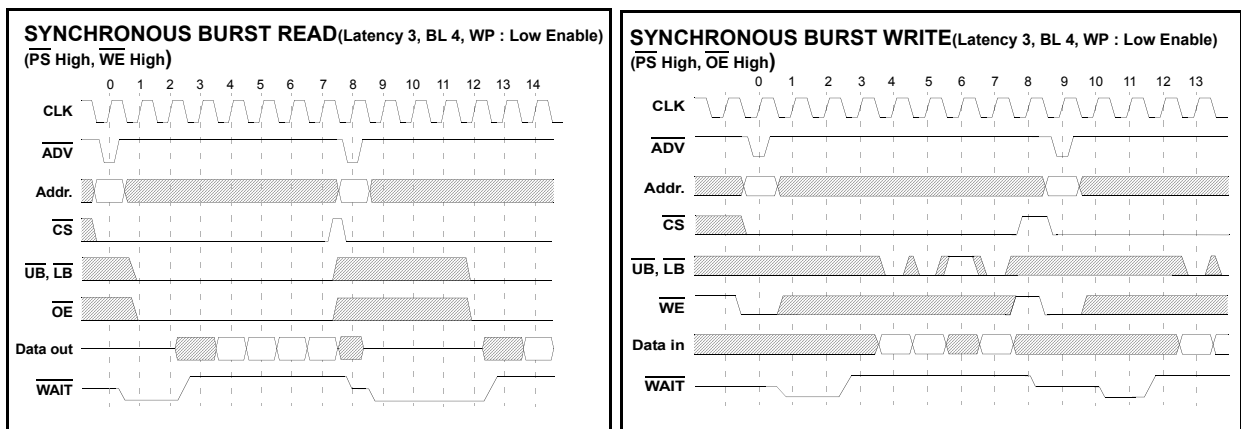
Synchronous Burst Read Operation

Burst Read command is implemented when \overline{ADV} is detected low at clock rising edge. \overline{WE} should be de-asserted during Burst read, Burst Read operation re-starts whenever \overline{ADV} is detected low at clock rising edge even in the middle of Burst Read operation. Variable latency allows the UTRAM to be configured for minimum latency at high frequencies, but the controller must monitor \overline{WAIT} to detect any conflict with refresh cycles.

Synchronous Burst Write Operation

Burst Write command is implemented when \overline{ADV} & \overline{WE} are detected low at clock rising edge. Burst Write operation re-starts whenever \overline{ADV} is detected low at clock rising edge even in the middle of Burst Write operation.

Write operations always use fixed latency.



FUNCTIONAL DESCRIPTION

\overline{CS}	\overline{PS}	\overline{OE}	\overline{WE}	\overline{LB}	\overline{UB}	I/O ₀₋₇	I/O ₈₋₁₅	CLK	\overline{ADV}	Mode	Power
H	H	X ¹⁾	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	High-Z	X ¹⁾	X ¹⁾	Deselected	Standby
H	L	X ¹⁾	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	High-Z	X ¹⁾	X ¹⁾	Deselected	PAR
L	H	H	H	X ¹⁾	X ¹⁾	High-Z	High-Z	X ¹⁾	H	Output Disabled	Active
L	H	X ¹⁾	X ¹⁾	H	H	High-Z	High-Z	X ¹⁾	H	Output Disabled	Active
L	H	X ¹⁾	H	X ¹⁾	X ¹⁾	High-Z	High-Z			Read Command	Active
L	H	L	H	L	H	Dout	High-Z		H	Lower Byte Read	Active
L	H	L	H	H	L	High-Z	Dout		H	Upper Byte Read	Active
L	H	L	H	L	L	Dout	Dout		H	Word Read	Active
L	H	X ¹⁾	L	X ¹⁾	X ¹⁾	High-Z	High-Z			Write Command	Active
L	H	H	X ¹⁾	L	H	Din	High-Z		H	Lower Byte Write	Active
L	H	H	X ¹⁾	H	L	High-Z	Din		H	Upper Byte Write	Active
L	H	H	X ¹⁾	L	L	Din	Din		H	Word Write	Active
L	L	H	L	L	L	High-Z	High-Z			Mode Register Set	Active

1. X means "Don't care". X should be low or high state.

2. \overline{WAIT} is device output signal so does not have any affect to the mode definition. Please refer to each timing diagram for \overline{WAIT} pin function.

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MODE 1 AC OPERATING CONDITIONS (ASYNCH. READ / ASYNCH. WRITE)

TEST CONDITIONS

(Test Load and Test Input/Output Reference)

Input pulse level: 0.2 to V_{CCQ}-0.2V

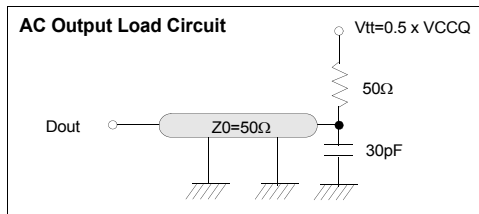
Input rising and falling time: 3ns

Input and output reference voltage: 0.5 x V_{CCQ}

Output load: CL=30pF

V_{CC}: 1.7V~1.95V

T_A: -40°C~85°C



AC CHARACTERISTICS

Parameter List		Symbol	Speed		Units
			Min	Max	
Common	\overline{CS} High Pulse Width	t _{CSHP(A)}	10	-	ns
Asynch. Read	Read Cycle Time	t _{RC}	70	-	ns
	Page Read Cycle Time	t _{PC}	20	-	ns
	Address Access Time	t _{AA}	-	70	ns
	Page Access Time	t _{PA}	-	20	ns
	Chip Select to Output	t _{CO}	-	70	ns
	Output Enable to Valid Output	t _{OE}	-	20	ns
	\overline{UB} , \overline{LB} Access Time	t _{BA}	-	20	ns
	Chip Select to Low-Z Output	t _{LZ}	10	-	ns
	\overline{UB} , \overline{LB} Enable to Low-Z Output	t _{BLZ}	5	-	ns
	Output Enable to Low-Z Output	t _{OLZ}	5	-	ns
	Chip Disable to High-Z Output	t _{CHZ}	0	10	ns
	\overline{UB} , \overline{LB} Disable to High-Z Output	t _{BHZ}	0	10	ns
	Output Disable to High-Z Output	t _{OHZ}	0	10	ns
	Output Hold	t _{OH}	5	-	ns
Asynch. Write	Write Cycle Time	t _{WC}	70	-	ns
	Chip Select to End of Write	t _{CW}	60	-	ns
	Address Set-up Time to Beginning of Write	t _{AS}	0	-	ns
	Address Valid to End of Write	t _{AW}	60	-	ns
	\overline{UB} , \overline{LB} Valid to End of Write	t _{BW}	60	-	ns
	Write Pulse Width	t _{WP}	55 ¹⁾	-	ns
	\overline{WE} High Pulse Width	t _{WHP}	5	-	ns
	Write Recovery Time	t _{WR}	0	-	ns
	Data to Write Time Overlap	t _{DW}	20	-	ns
	Data Hold from Write Time	t _{DH}	0	-	ns

1. t_{WP}(min)=70ns for continuous write without CS toggling longer than 1.7us

2. The High-Z timings measure a 100mV transition from either V_{OH} or V_{OL} toward V_{CCQ} x 0.5

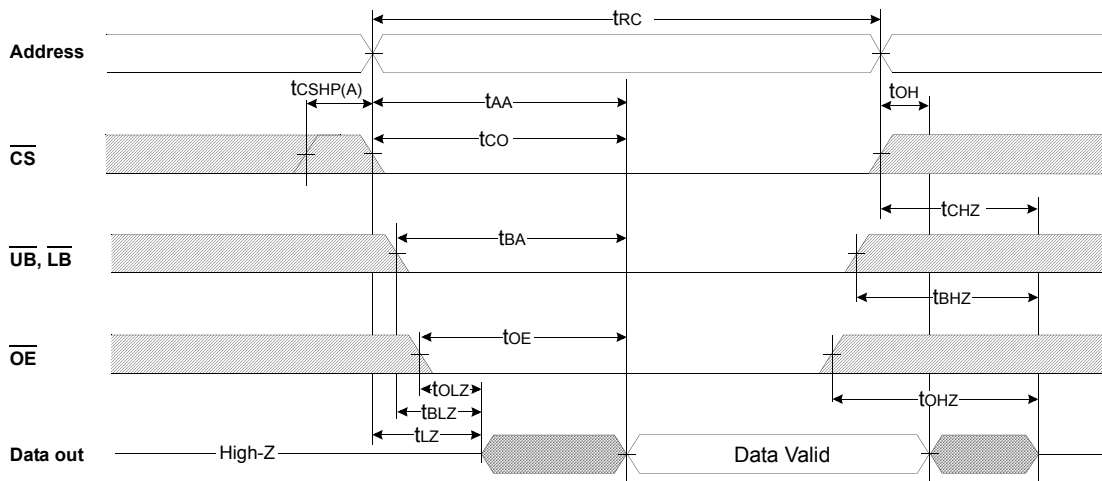
3. The Low-Z timings measure a 100mV transition away from the High-Z level toward either V_{OH} or V_{OL}.

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TIMING WAVEFORMS (ASYNCH. READ / ASYNCH. WRITE)

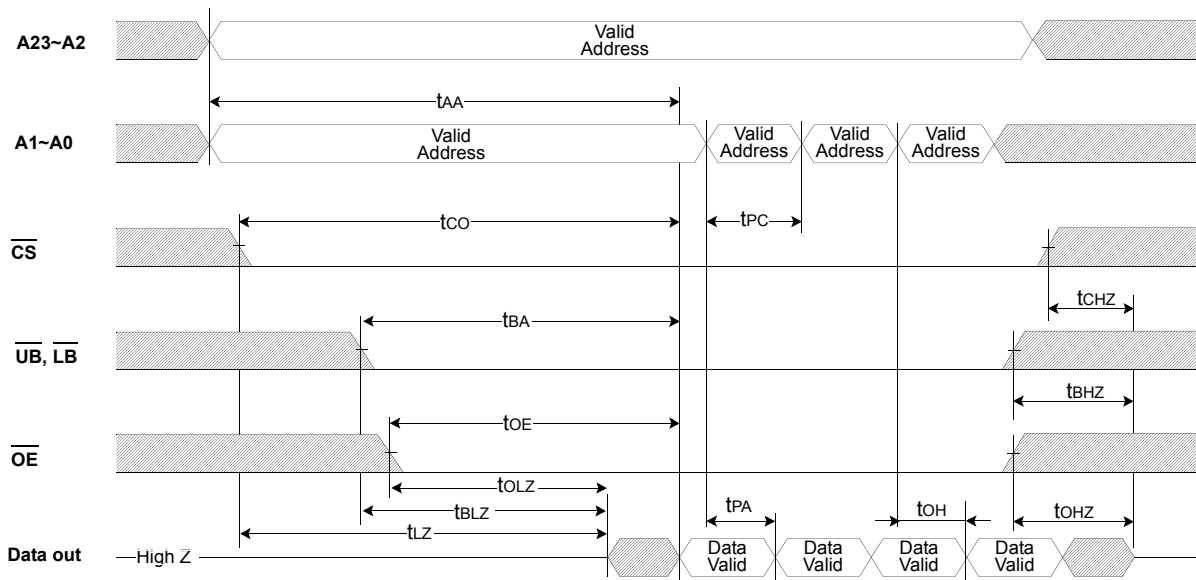
Asynch. READ

(PS=VIH, WE=VIH, WAIT=High-Z)



Asynch. PAGE READ

(PS=VIH, WE=VIH, WAIT=High-Z)

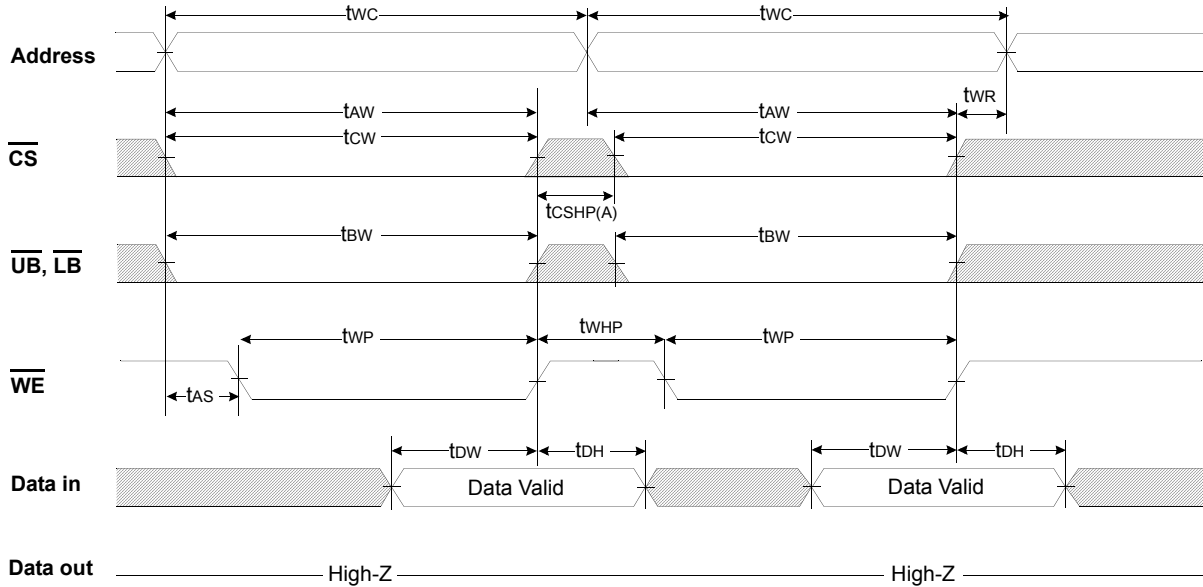


1. t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, $t_{CHZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device interconnection.
3. In asynchronous read cycle, Clock and \overline{ADV} signals are ignored.
4. If invalid address signals shorter than min. t_{RC} are continuously repeated for over 1.7 μs , the device needs a normal read timing(t_{RC}) or needs to sustain standby state for min. t_{RC} at least once in every 1.7 μs .
5. In asynchronous 4 page read cycle, Clock and \overline{ADV} signals are ignored.

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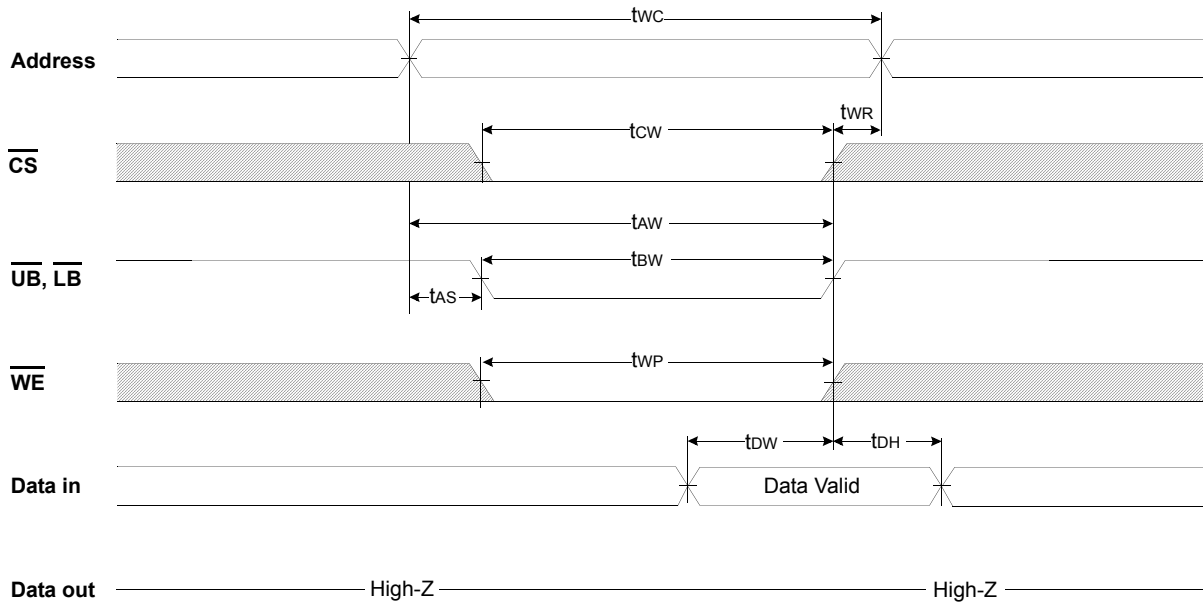
Asynch. WRITE (1)

(PS=VIH, OE=VIH, WAIT=High-Z, WE Controlled)



Asynch. WRITE (2)

(PS=VIH, OE=VIH, WAIT=High-Z, UB & LB Controlled)



1. A write occurs during the overlap(t_{WP}) of low \overline{CS} and low \overline{WE} . A write begins when \overline{CS} goes low and \overline{WE} goes low with asserting \overline{UB} or \overline{LB} for single byte operation or simultaneously asserting \overline{UB} and \overline{LB} for double byte operation. A write ends at the earliest transition when \overline{CS} goes high or \overline{WE} goes high. The t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the \overline{CS} going low to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. t_{WR} is applied in case a write ends with \overline{CS} or \overline{WE} going high.
5. In asynchronous write cycle, Clock and \overline{ADV} signals are ignored.
6. Condition for continuous write operation over 15 times : t_{WP(min)}=70ns

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MODE 2 AC OPERATING CONDITIONS (SYNCH. READ / ASYNCH. WRITE)

TEST CONDITIONS

(Test Load and Test Input/Output Reference)

Input pulse level: 0.2 to V_{CCQ}-0.2V

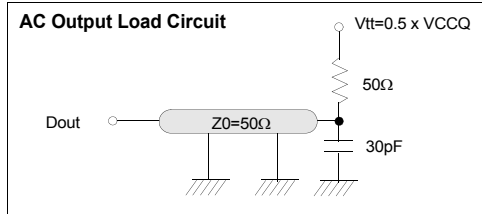
Input rising and falling time: 1ns

Input and output reference voltage: 0.5 x V_{CCQ}

Output load: CL=30pF

V_{CC}: 1.7V~1.95V

T_A: -40°C~85°C



AC CHARACTERISTICS

Parameter List	Symbol	66MHz		80MHz		104MHz		Units
		Min	Max	Min	Max	Min	Max	
Clock Cycle Time	T	15	200	12.5	200	9.6	200	ns
Burst Cycle Time	t _{BC}	-	1700	-	1700	-	1700	ns
Address Set-up Time to clock	t _{AS(B)}	3	-	3	-	3	-	ns
Address Hold Time from clock	t _{AH(B)}	2	-	2	-	2	-	ns
ADV Setup Time to clock	t _{ADVS}	3	-	3	-	3	-	ns
ADV Hold Time from clock	t _{ADVH}	2	-	2	-	2	-	ns
CS Setup Time to clock	t _{CSS(B)}	3	-	3	-	3	-	ns
CS High to ADV Low (Burst Stop)	t _{BsADV¹⁾}	0	-	0	-	0	-	ns
CS Low Hold Time from Clock(Burst Stop)	t _{CsLH}	2	-	2	-	2	-	ns
CS High Pulse Width	t _{CsHP}	5	-	5	-	5	-	ns
CS Low to WAIT Low	t _{WL}	-	12	-	12	-	12	ns
Clock to WAIT High	t _{WH}	-	11	-	9	-	7	ns
CS High to WAIT High-Z	t _{WZ}	-	10	-	10	-	10	ns
UB, LB Low to End of Latency Clock	t _{BEL}	20	-	20	-	20	-	ns
OE Low to End of Latency Clock	t _{OEL}	20	-	20	-	20	-	ns
UB, LB Low to Low-Z Output	t _{B LZ}	5	-	5	-	5	-	ns
OE Low to Low-Z Output	t _{O LZ}	5	-	5	-	5	-	ns
Clock Rising to Data Output	t _{CD}	-	11	-	9	-	7	ns
Output Hold from clock	t _{OH(B)}	2	-	2	-	2	-	ns
Burst End Clock to Output High-Z	t _{HZ}	-	10	-	10	-	10	ns
CS High to Output High-Z	t _{CHZ}	-	10	-	10	-	10	ns
OE High to Output High-Z	t _{OHZ}	-	10	-	10	-	10	ns
UB, LB High to Output High-Z	t _{BHZ}	-	10	-	10	-	10	ns

1. Refresh can not be implemented when t_{BsADV} is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.7us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for t_{BsADV}.

2. The High-Z timings measure a 100mV transition from either V_{OH} or V_{OL} toward V_{CCQ} x 0.5

3. The Low-Z timings measure a 100mV transition away from the High-Z level toward either V_{OH} or V_{OL}.

Parameter List	Symbol	Speed		Units
		Min	Max	
Write Cycle Time	t _{WC}	70	-	
Chip Select to End of Write	t _{CW}	60	-	ns
ADV Minimum Low Pulse Width	t _{ADV}	5	-	ns
Address Set-up Time to Beginning of Write	t _{AS}	0	-	ns
Address Set-up Time to ADV Rising	t _{AS(A)}	5	-	ns
Address Hold Time from ADV Rising	t _{AH(A)}	3	-	ns
CS Setup Time to ADV Rising	t _{CSS(A)}	5	-	ns
Address Valid to End of Write	t _{AW}	60	-	ns
UB, LB Valid to End of Write	t _{BW}	60	-	ns
Write Pulse Width	t _{WP}	55 ¹⁾	-	ns
Write Recovery Time	t _{WR}	0	-	ns
Data to Write Time Overlap	t _{DW}	20	-	ns
Data Hold from Write Time	t _{DH}	0	-	ns

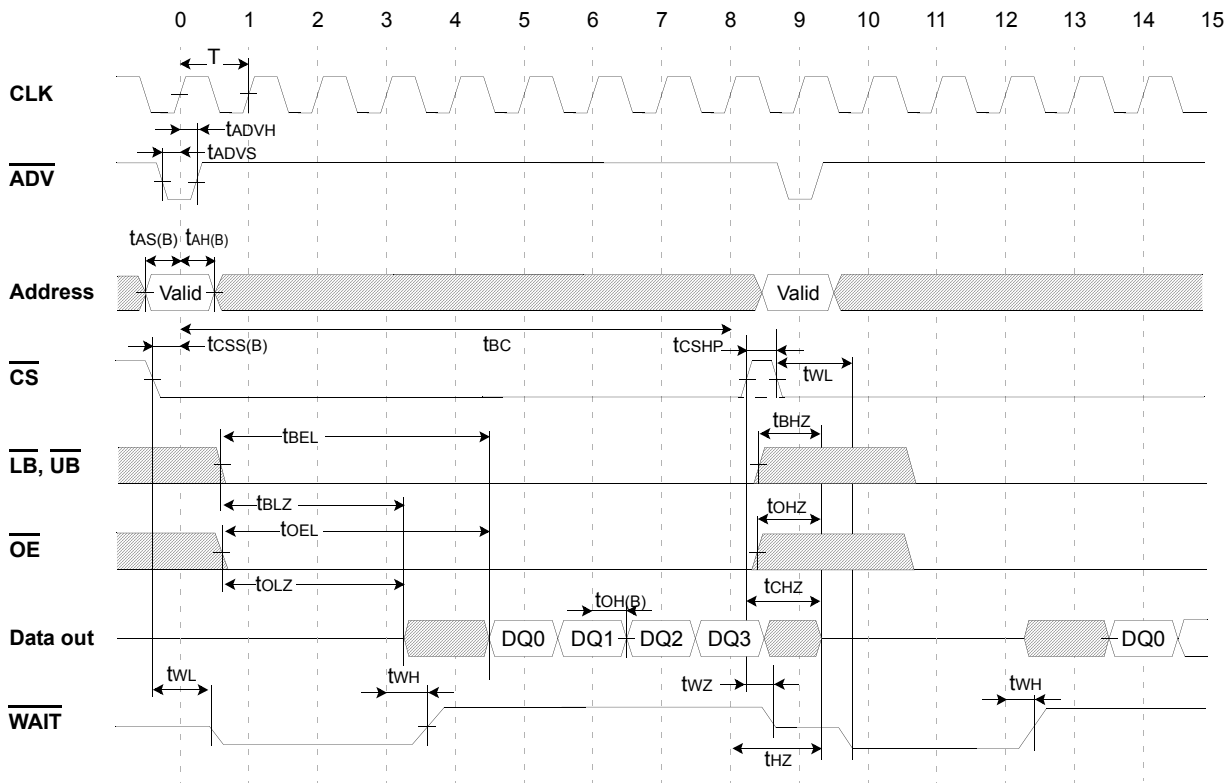
1. t_{WP}(min)=70ns for continuous write longer than 1.7us without CS toggling.

K1B5616B2M

TIMING WAVEFORMS (SYNCH. READ / ASYNCH. WRITE)

Burst READ - Fixed Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



1. /WAIT Low(t_{WL}) : Data not available(driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 /WAIT High(t_{WH}) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(t_{WZ}) : Data don't care(driven by \overline{CS} high going edge)
2. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than t_{BC} (1.7 μ s)

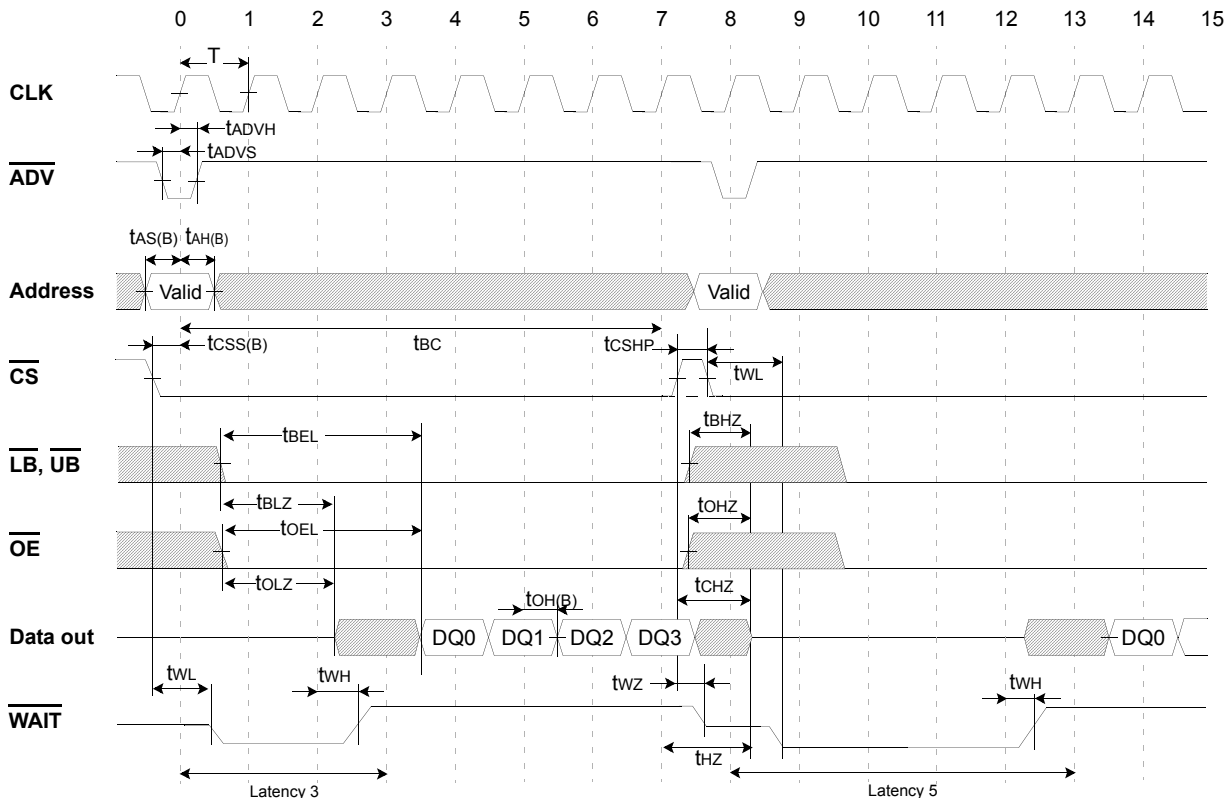
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1700	-	1700	-	1700	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	toHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tcSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tcSHP	5	-	5	-	5	-	ns	toH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	twL	-	12	-	12	-	12	ns
toEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
twZ	-	10	-	10	-	10	ns								

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Burst READ - Variable Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=3, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



1. Delayed Latency should be taken increased when refresh is required. Refer to Latency Table.
2. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(twz) : Data don't care(driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than tBC(1.7µs)

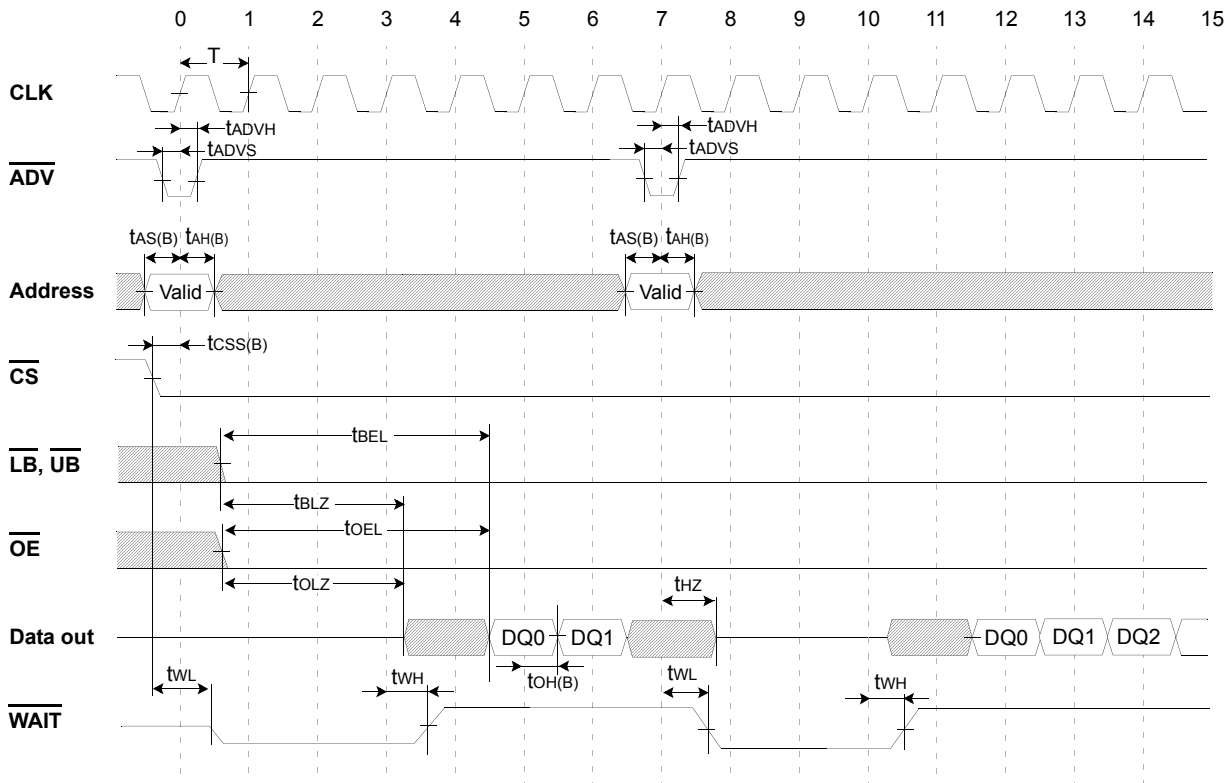
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1700	-	1700	-	1700	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
twz	-	10	-	10	-	10	ns								

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Burst READ (\overline{ADV} Interrupt) - Fixed Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



1. Refresh is blocked during \overline{ADV} Interrupt Read and continuous Burst Read by \overline{ADV} interrupt should not be longer than tBC (1.7us)
2. /WAIT Low(tWL) : Data not available(driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(tWZ) : Data don't care(driven by \overline{CS} high going edge)
3. Multiple clock risings are allowed during low \overline{ADV} period but the First valid data come out after set Latency from the last clock rising.
4. Burst interrupt is allowable after the first data received by controller.

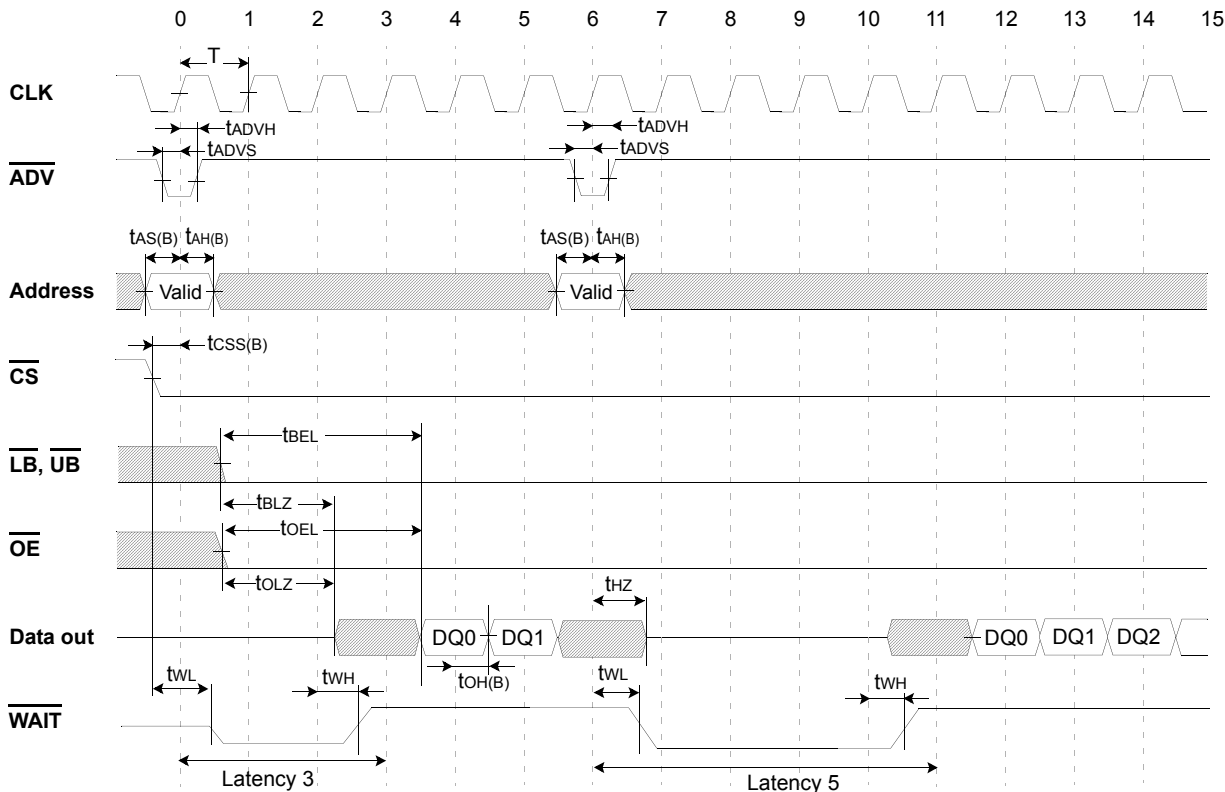
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1700	-	1700	-	1700	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

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Burst READ (ADV Interrupt) - Variable Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=3, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



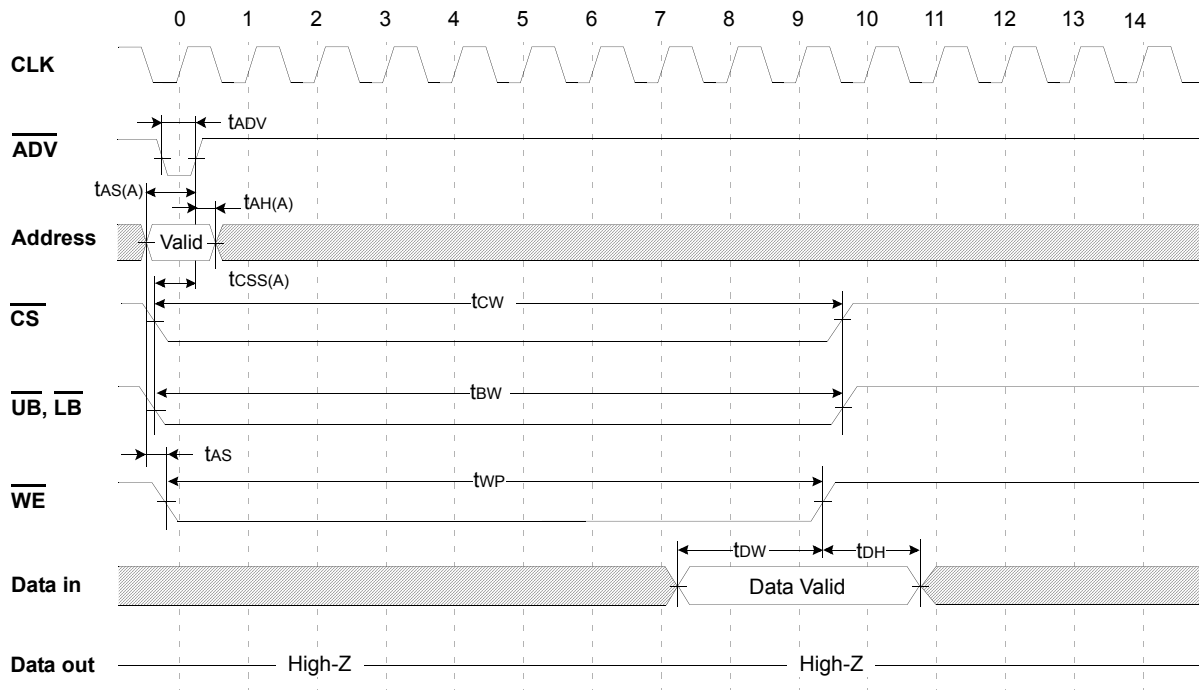
1. Delayed Latency should be taken increased when refresh is required. Refer to Latency Table.
2. Refresh is blocked during ADV Interrupt Read and continuous Burst Read by ADV interrupt should not be longer than tBC (1.7us)
3. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
4. Multiple clock risings are allowed during low ADV period but the First valid data come out after set Latency from the last clock rising.
5. Burst interrupt is allowable after the first data received by controller.

AC CHARACTERISTICS

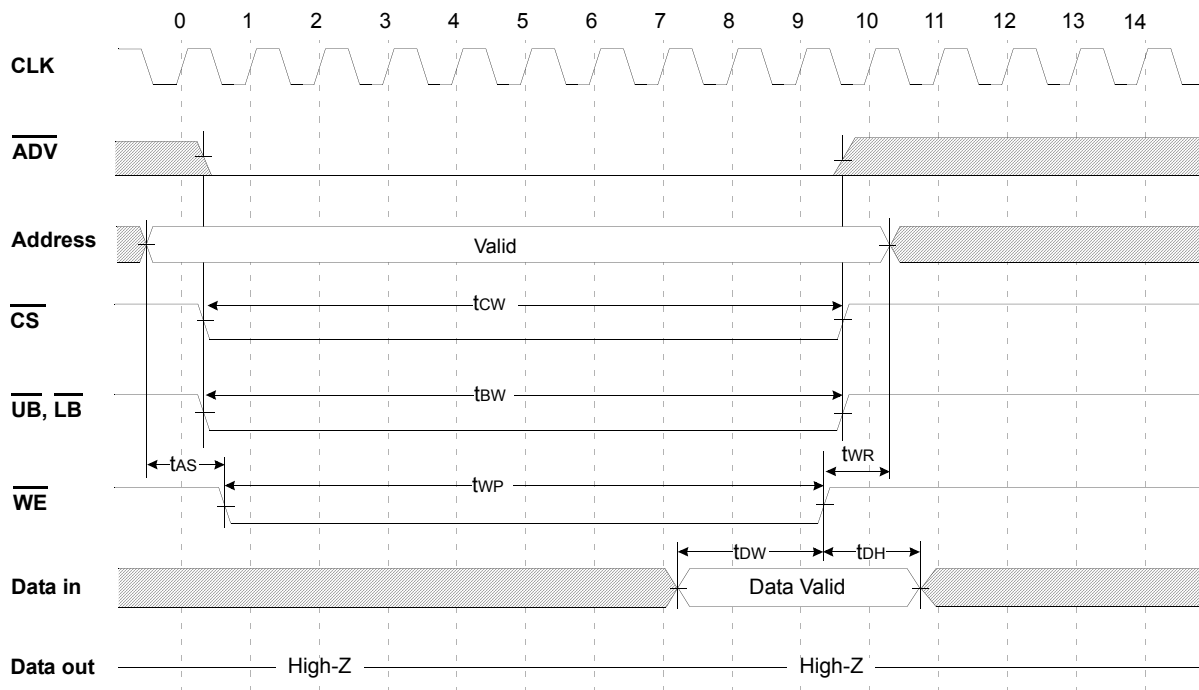
Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1700	-	1700	-	1700	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

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Asynch. WRITE (ADV Latch)
 (PS=VIH, OE=VIH, WAIT=High-Z)

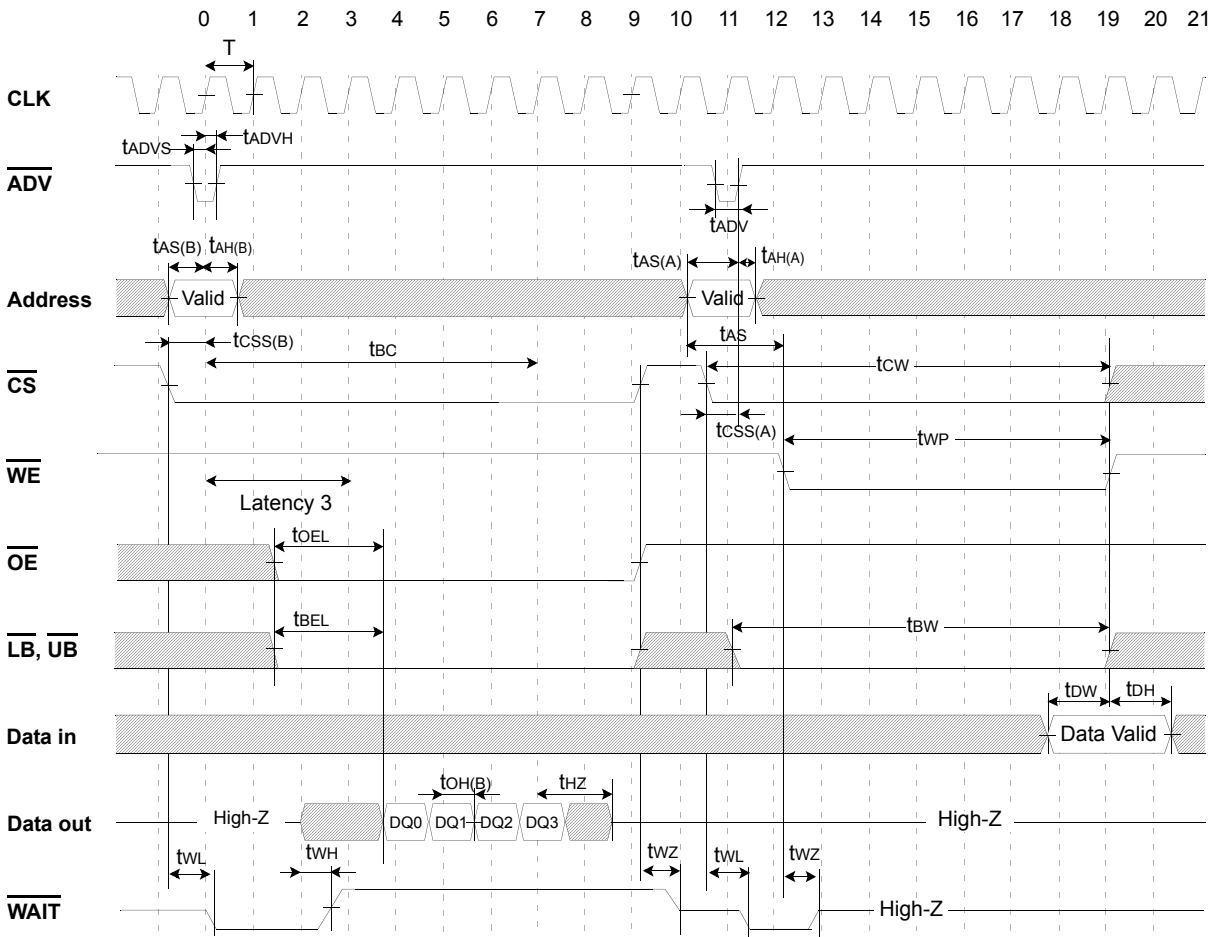


Asynch. WRITE (\overline{ADV} Fix Low)
 (PS=VIH, OE=VIH, WAIT=High-Z)



K1B5616B2M

Burst READ followed by Asynch. WRITE
 (PS=VIH, WAIT=High-Z, Variable Latency=3)

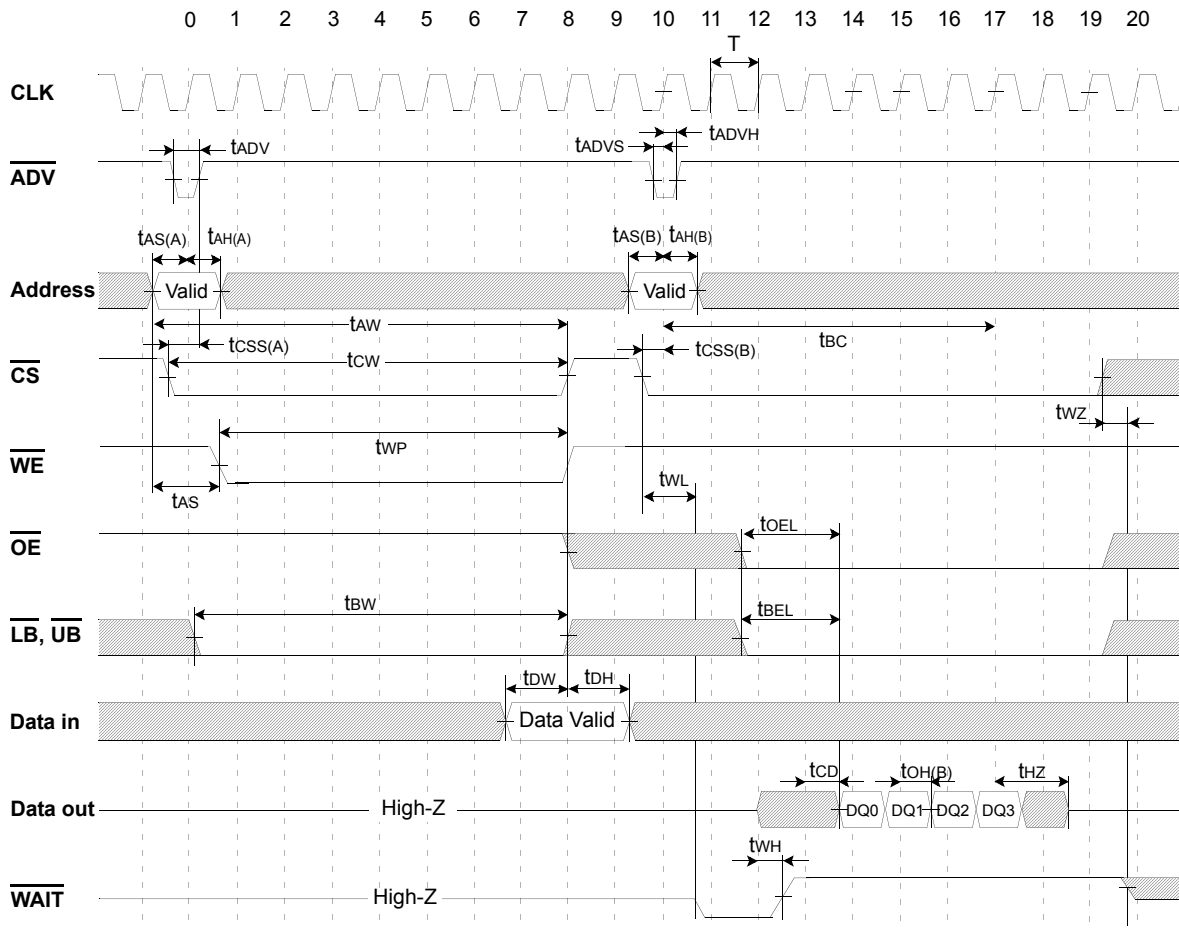


1. A write occurs during the overlap (t_{WP}) of low \overline{CS} and low \overline{WE} . A write begins when \overline{CS} goes low and \overline{WE} goes low with asserting \overline{UB} or \overline{LB} for single byte operation or simultaneously asserting \overline{UB} and \overline{LB} for word operation. A write ends at the earliest transition when \overline{CS} goes high or \overline{WE} goes high. The t_{WP} is measured from the beginning of write to the end of write.
2. t_{W} is measured from the address valid to the end of write. In this address latch type write timing, t_{WC} is same as t_{W} .
3. t_{CW} is measured from the \overline{CS} going low to the end of write.
4. t_{W} is measured from the \overline{UB} and \overline{LB} going low to the end of write.

K1B5616B2M

Asynch. WRITE followed by Burst READ

(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



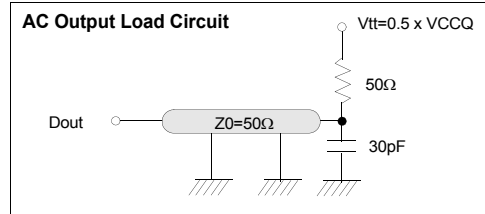
1. /WAIT Low(tWL) : Data not available(driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(tWZ) : Data don't care(driven by \overline{CS} high going edge)
2. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than tBC(1.7 μ s)

K1B5616B2M

MODE 3 AC OPERATING CONDITIONS (SYNCH. READ / SYNCH. WRITE)

TEST CONDITIONS

(Test Load and Test Input/Output Reference)
 Input pulse level: 0.2 to Vcc-0.2V
 Input rising and falling time: 1ns
 Input and output reference voltage: 0.5 x Vcc
 Output load: CL=30pF
 Vcc: 1.7V~1.95V
 TA: -40°C~85°C



AC CHARACTERISTICS

Parameter List		Symbol	66MHz		80MHz		104MHz		Units
			Min	Max	Min	Max	Min	Max	
Burst Operation (Common)	Clock Cycle Time	T	15	200	12.5	200	9.6	200	ns
	Burst Cycle Time	tBC	-	1700	-	1700	-	1700	ns
	Address Set-up Time to clock	tAS(B)	3	-	3	-	3	-	ns
	Address Hold Time from clock	tAH(B)	2	-	2	-	2	-	ns
	\overline{ADV} Setup Time to clock	tADVS	3	-	3	-	3	-	ns
	\overline{ADV} Hold Time from clock	tADVH	2	-	2	-	2	-	ns
	\overline{CS} Setup Time to clock	tCSS(B)	3	-	3	-	3	-	ns
	\overline{CS} High to New \overline{ADV} Low (Burst Stop)	tBSADV	0	-	0	-	0	-	ns
	\overline{CS} Low Hold Time from Clock(Burst Stop)	tCSLH	2	-	2	-	2	-	ns
	\overline{CS} High Pulse Width	tCSHP	5	-	5	-	5	-	ns
	\overline{CS} Low to \overline{WAIT} Low	tWL	-	12	-	12	-	12	ns
	Clock to \overline{WAIT} High	tWH	-	11	-	9	-	7	ns
\overline{CS} High to \overline{WAIT} High-Z	tWZ	-	10	-	10	-	10	ns	
Burst Read Operation	$\overline{UB}, \overline{LB}$ Low to End of Latency Clock	tBEL	20	-	20	-	20	-	ns
	\overline{OE} Low to End of Latency Clock	toEL	20	-	20	-	20	-	ns
	$\overline{UB}, \overline{LB}$ Low to Low-Z Output	tBLZ	5	-	5	-	5	-	ns
	\overline{OE} Low to Low-Z Output	toLZ	5	-	5	-	5	-	ns
	Clock Rising to Data Output	tCD	-	11	-	9	-	7	ns
	Output Hold from clock	tOH(B)	2	-	2	-	2	-	ns
	Burst End Clock to Output High-Z	tHZ	-	10	-	10	-	10	ns
	\overline{CS} High to Output High-Z	tCHZ	-	10	-	10	-	10	ns
	\overline{OE} High to Output High-Z	toHZ	-	10	-	10	-	10	ns
$\overline{UB}, \overline{LB}$ High to Output High-Z	tBHZ	-	10	-	10	-	10	ns	

1. Refresh can not be implemented when tBSADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.7us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBSADV.
2. The High-Z timings measure a 100mV transition from either VOH or VOL toward VCCQ x 0.5
3. The Low-Z timings measure a 100mV transition away from the High-Z level toward either VOH or VOL.

Burst Write Operation	\overline{WE} Set-up Time to Clock	tWES	3	-	3	-	3	-	ns
	\overline{WE} Hold Time from Clock	tWEH	2	-	2	-	2	-	ns
	$\overline{UB}, \overline{LB}$ Set-up Time to Clock	tBS	3	-	3	-	3	-	ns
	Burst End clock to New \overline{ADV} Low	tBEADV	0	-	0	-	0	-	ns
	$\overline{UB}, \overline{LB}$ Hold Time from Clock	tBH	2	-	2	-	2	-	ns
	Byte Masking Set-up Time to Clock	tBMS	3	-	3	-	3	-	ns
	Byte Masking Hold Time from Clock	tBMH	2	-	2	-	2	-	ns
	Write Data Set-up Time to Clock	tDS	3	-	3	-	3	-	ns
Write Data Hold Time from Clock	tDHC	2	-	2	-	2	-	ns	

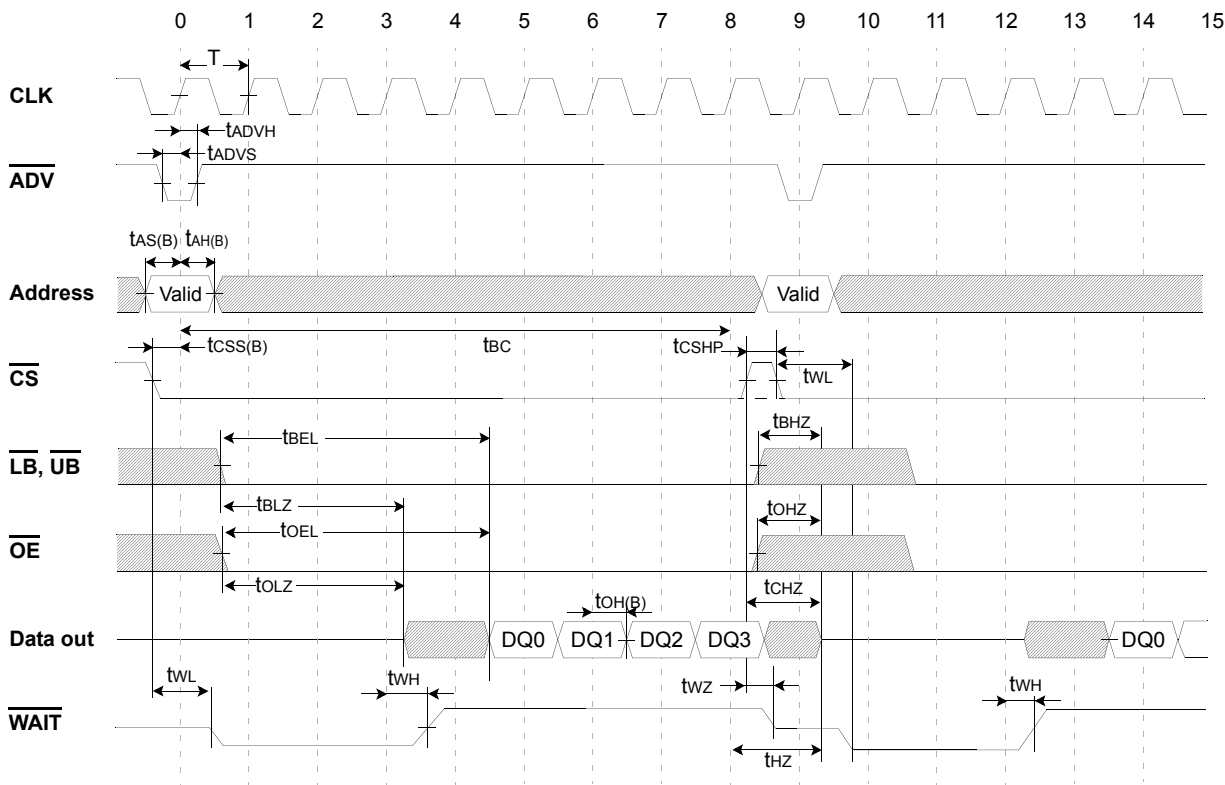
1. Refresh can not be implemented when tBEADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.7us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBEADV.

K1B5616B2M

TIMING WAVEFORMS (SYNCH. READ / SYNCH. WRITE)

Burst READ - Fixed Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



1. /WAIT Low(t_{WL}) : Data not available(driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 /WAIT High(t_{WH}) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(t_{WZ}) : Data don't care(driven by \overline{CS} high going edge)
2. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than t_{BC} (1.7 μ s)

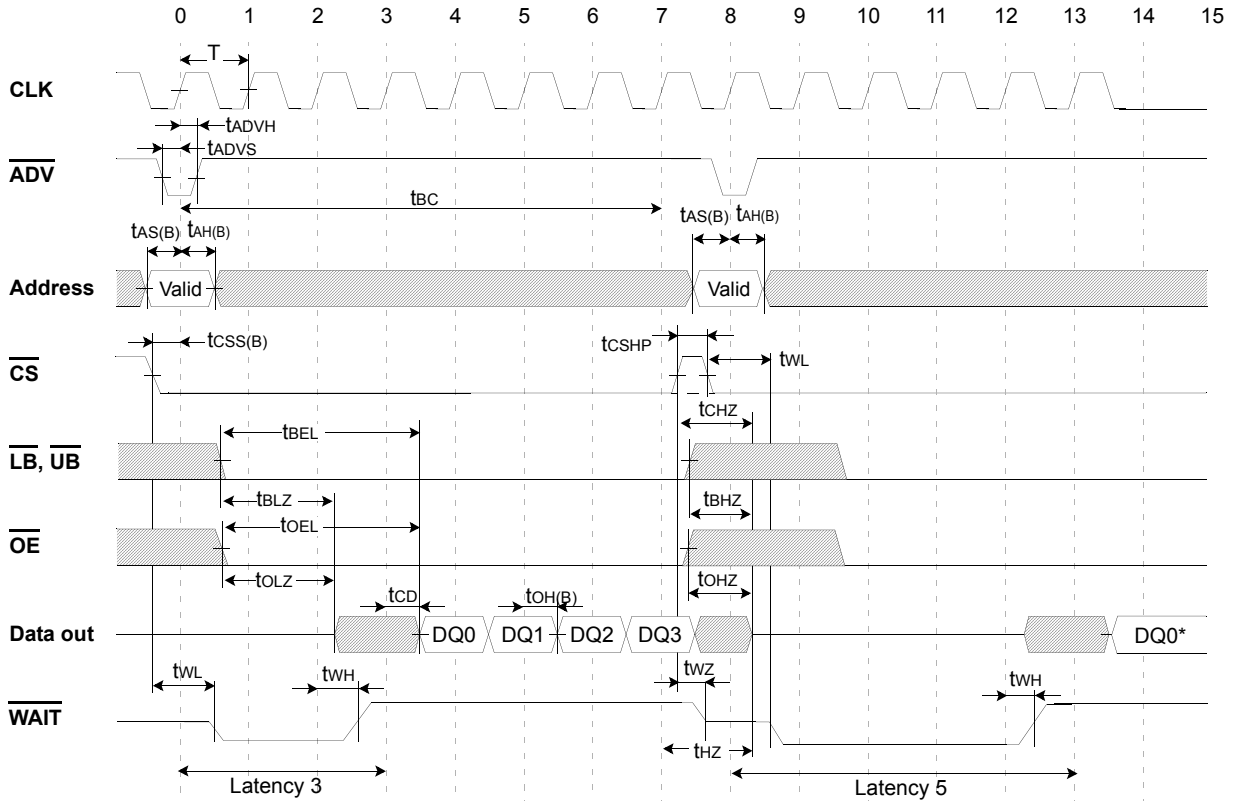
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1700	-	1700	-	1700	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tcSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
twZ	-	10	-	10	-	10	ns								

K1B5616B2M

Burst READ - Variable Latency

(PS=VIH, WE=VIH, Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



1. Delayed Latency should be taken increased when refresh is required. Refer to Latency Table.
2. /WAIT Low (tWL) : Data not available (driven by CS low going edge or ADV low going edge)
 /WAIT High (tWH) : Data available (driven by Latency-1 clock)
 /WAIT High-Z (tWZ) : Data don't care (driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than tBC (1.7µs).

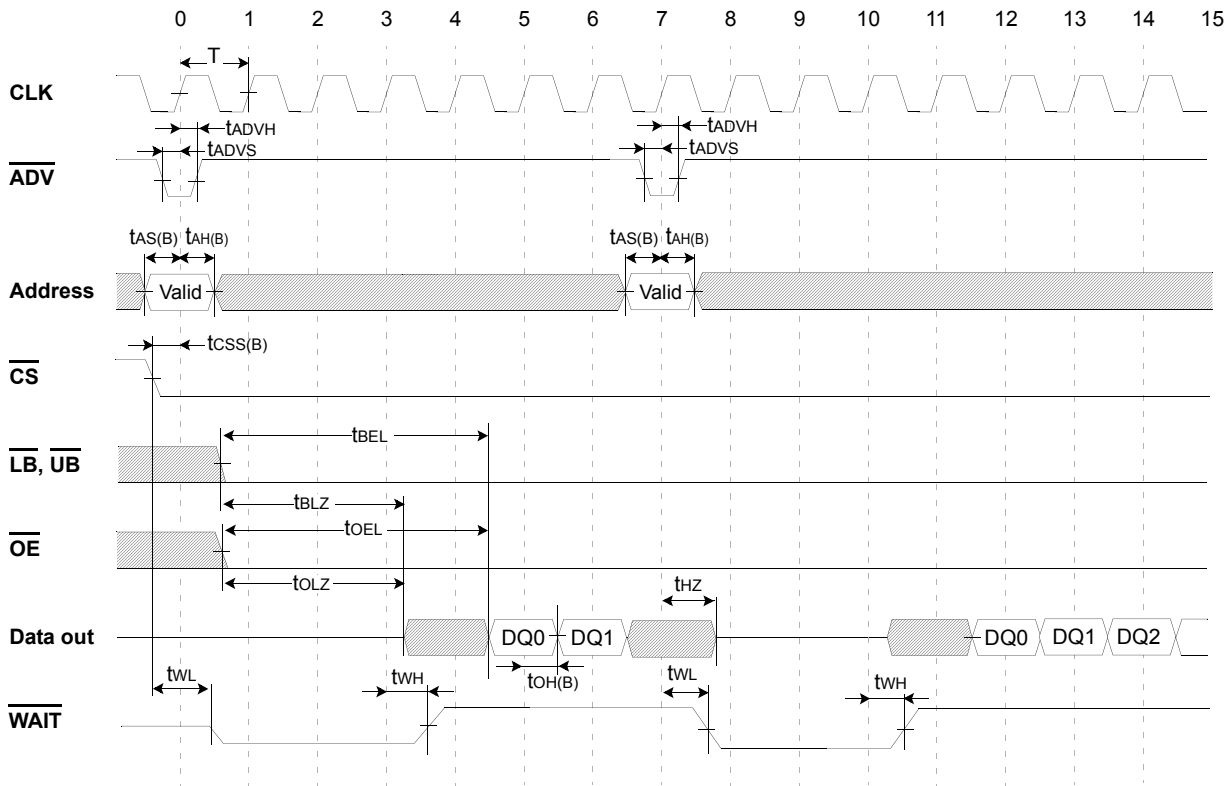
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1700	-	1700	-	1700	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

K1B5616B2M

Burst READ (\overline{ADV} Interrupt) - Fixed Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



1. Refresh is blocked during \overline{ADV} Interrupt Read and continuous Burst Read by \overline{ADV} interrupt should not be longer than tBC (1.7us)
2. /WAIT Low(tWL) : Data not available(driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(tWZ) : Data don't care(driven by \overline{CS} high going edge)
3. Multiple clock risings are allowed during low \overline{ADV} period but the First valid data come out after set Latency from the last clock rising.
4. Burst interrupt is allowable after the first data received by controller.

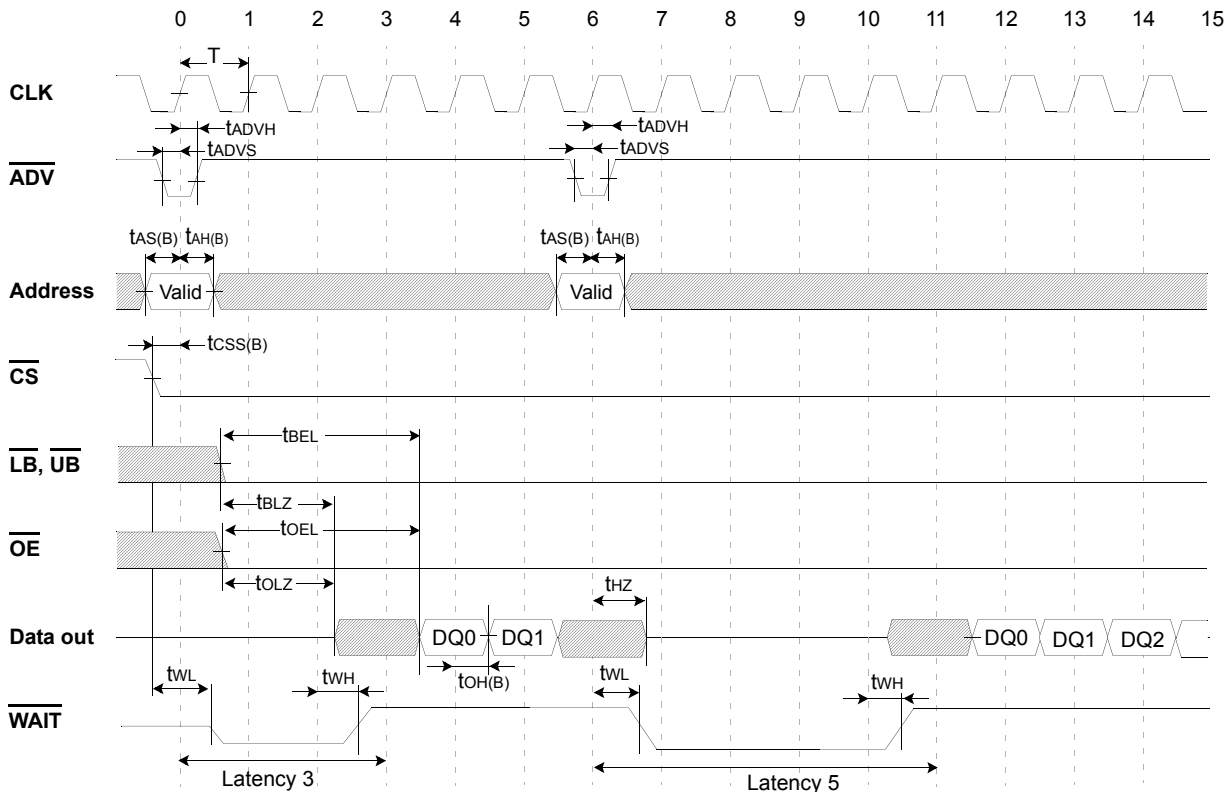
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1700	-	1700	-	1700	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tcSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tcSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

K1B5616B2M

Burst READ (ADV Interrupt) - Variable Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=3,Burst Length=4,WP=Low enable, WC=one clock prior to the data)



1. Delayed latency is taken for Burst READ by \overline{ADV} interrupt. Refer to Latency Table.
2. Refresh is blocked during \overline{ADV} Interrupt Read and continuous Burst Read by \overline{ADV} interrupt should not be longer than t_{BC} (1.7us)
3. /WAIT Low(t_{WL}) : Data not available(driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 /WAIT High(t_{WH}) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(t_{WZ}) : Data don't care(driven by \overline{CS} high going edge)
4. Multiple clock risings are allowed during low \overline{ADV} period. The data come out after set Latency from the last clock rising.
5. Burst interrupt is allowable after the first data received by controller.

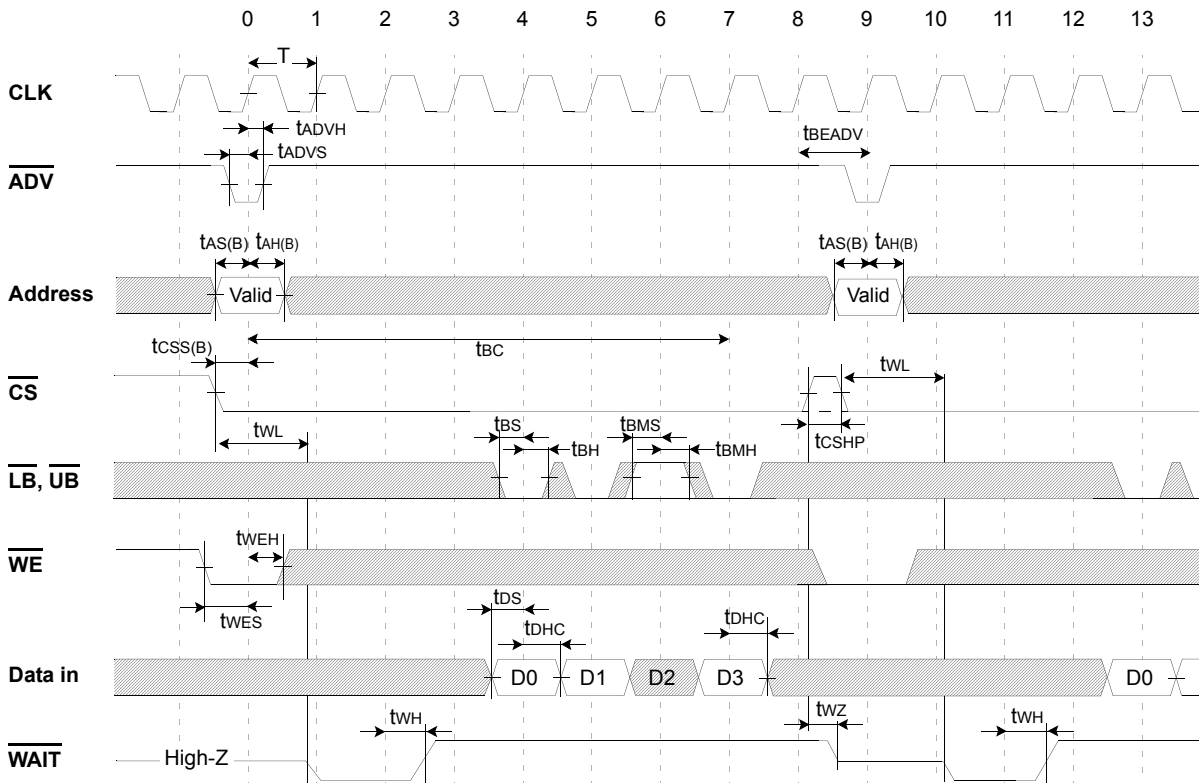
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	t_{BLZ}	5	-	5	-	5	-	ns
t_{BC}	-	1700	-	1700	-	1700	ns	t_{OLZ}	5	-	5	-	5	-	ns
t_{ADVS}	3	-	3	-	3	-	ns	t_{HZ}	-	10	-	10	-	10	ns
t_{ADVH}	2	-	2	-	2	-	ns	t_{CHZ}	-	10	-	10	-	10	ns
$t_{AS(B)}$	3	-	3	-	3	-	ns	t_{OHZ}	-	10	-	10	-	10	ns
$t_{AH(B)}$	2	-	2	-	2	-	ns	t_{BHZ}	-	10	-	10	-	10	ns
$t_{CSS(B)}$	3	-	3	-	3	-	ns	t_{CD}	-	11	-	9	-	7	ns
t_{CSHP}	5	-	5	-	5	-	ns	$t_{OH(B)}$	2	-	2	-	2	-	ns
t_{BEL}	20	-	20	-	20	-	ns	t_{WL}	-	12	-	12	-	12	ns
t_{OEL}	20	-	20	-	20	-	ns	t_{WH}	-	11	-	9	-	7	ns
t_{WZ}	-	10	-	10	-	10	ns								

K1B5616B2M

Burst WRITE

(PS=VIH, OE=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



1. Refresh can not be implemented when tBEADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.7us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBEADV.
2. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising. The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than tBC(1.7us)

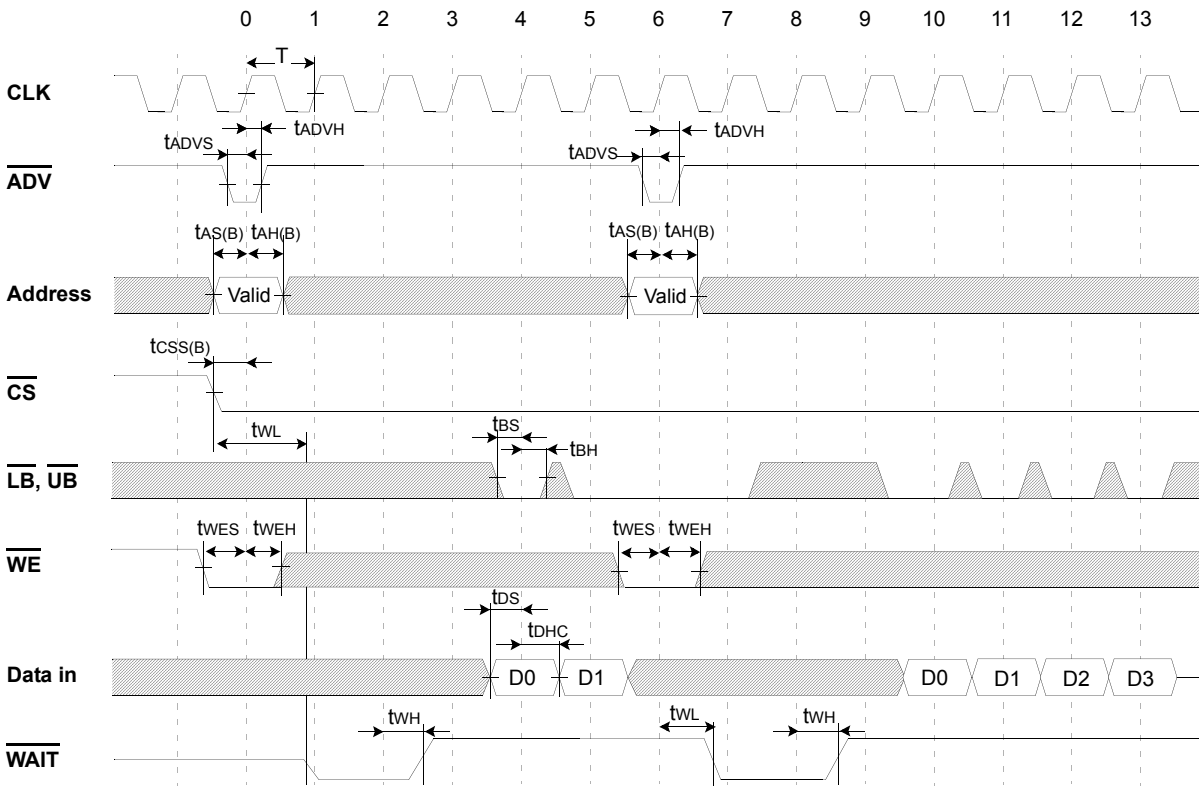
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
tCSHP	5	-	5	-	5	-	ns	tDS	3	-	3	-	3	-	ns
tBS	3	-	3	-	3	-	ns	tDHC	2	-	2	-	2	-	ns
tBH	2	-	2	-	2	-	ns	tWL	-	12	-	12	-	12	ns
tBMS	3	-	3	-	3	-	ns	tWH	-	11	-	9	-	7	ns
tBMH	2	-	2	-	2	-	ns	tWZ	-	10	-	10	-	10	ns
tWES	3	-	3	-	3	-	ns								
tWEH	2	-	2	-	2	-	ns								

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Burst WRITE (ADV PULSE Interrupt)

(PS=VIH, OE=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



- Multiple clock risings are allowed during low \overline{ADV} period. The data starts after set Latency from the last clock rising.
- \overline{WAIT} Low (t_{WL}): Data not available (driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 \overline{WAIT} High (t_{WH}): Data available (driven by Latency-1 clock)
 \overline{WAIT} High-Z (t_{WZ}): Data don't care (driven by \overline{CS} high going edge)
- Burst interrupt is allowable after the first data word written.

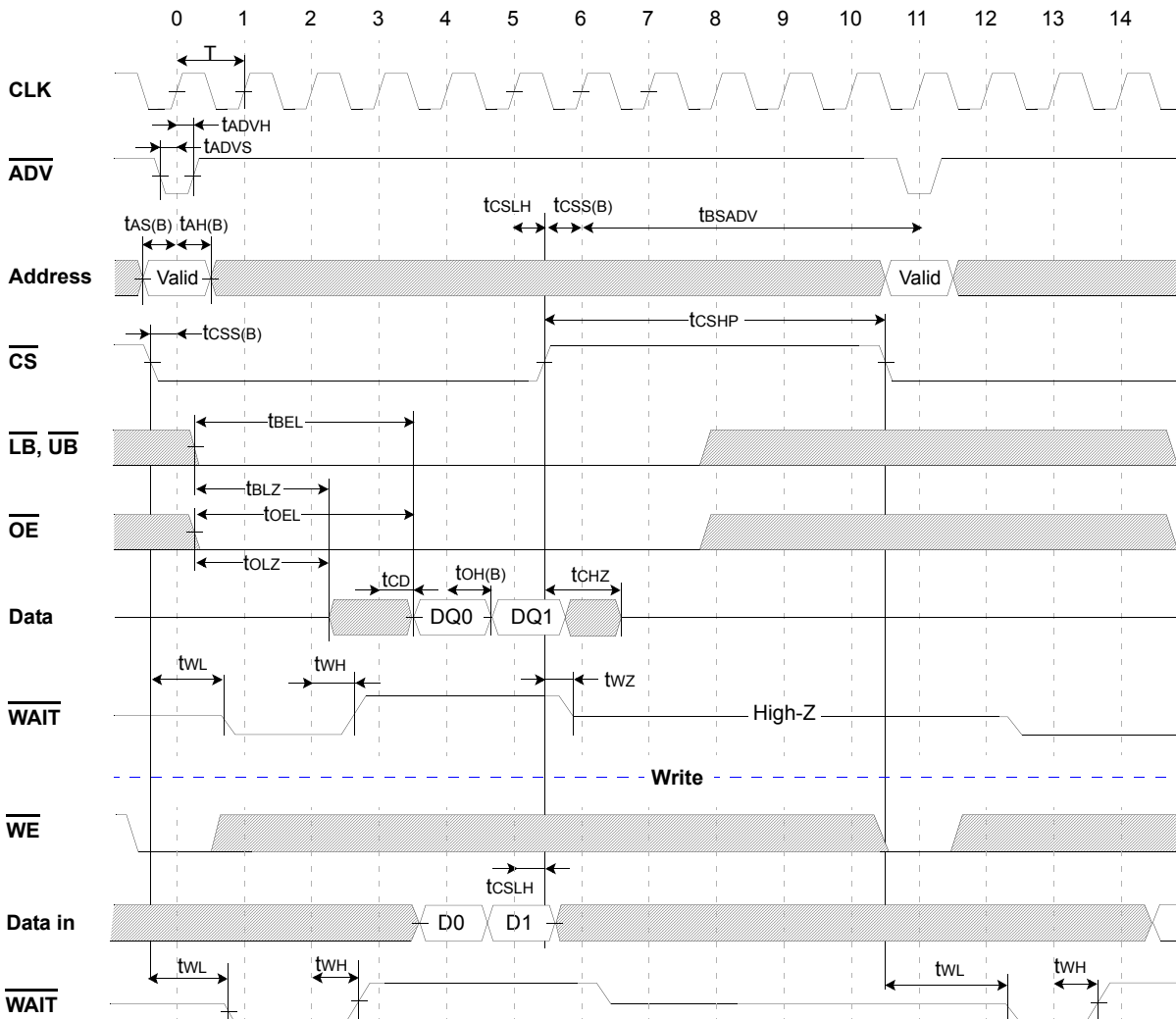
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
t_{CSHP}	5	-	5	-	5	-	ns	t_{DS}	3	-	3	-	3	-	ns
t_{BS}	3	-	3	-	3	-	ns	t_{DHC}	2	-	2	-	2	-	ns
t_{BH}	2	-	2	-	2	-	ns	t_{WL}	-	12	-	12	-	12	ns
t_{BMS}	3	-	3	-	3	-	ns	t_{WH}	-	11	-	9	-	7	ns
t_{BMH}	2	-	2	-	2	-	ns	t_{WZ}	-	10	-	10	-	10	ns
t_{WES}	3	-	3	-	3	-	ns								
t_{WEH}	2	-	2	-	2	-	ns								

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Burst READ STOP & Burst WRITE STOP

(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



1. Refresh can not be implemented when t_{BEADV} is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.7us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for t_{BEADV} .
2. Multiple clock risings are allowed during low \overline{ADV} period. The data starts after set Latency from the last clock rising.
3. \overline{WAIT} Low(t_{WL}) : Data not available(driven by \overline{CS} low going edge or \overline{ADV} low going edge)
 \overline{WAIT} High(t_{WH}) : Data available(driven by Latency-1 clock)
 \overline{WAIT} High-Z(t_{WZ}) : Data don't care(driven by \overline{CS} high going edge)

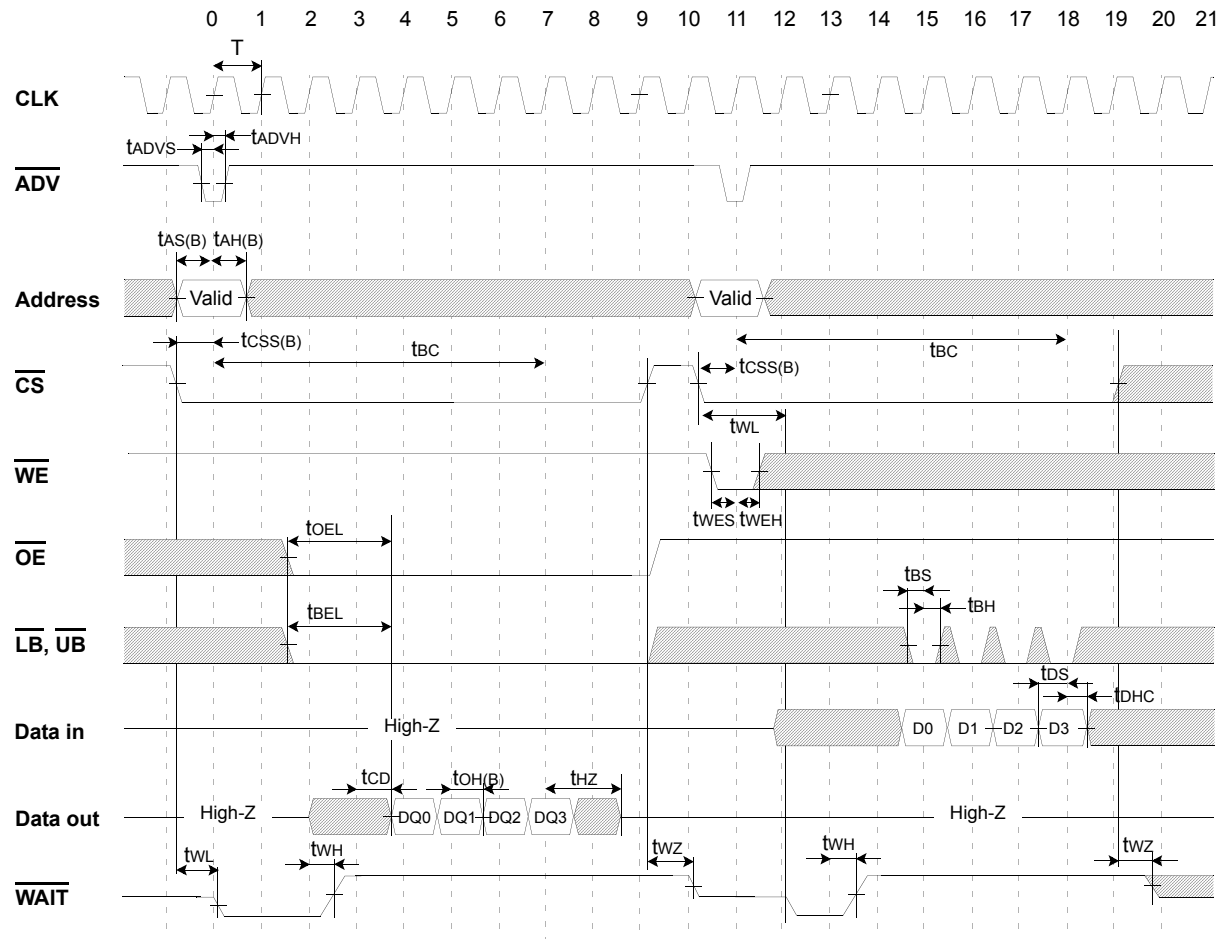
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
t_{CSHP}	5	-	5	-	5	-	ns	t_{DS}	3	-	3	-	3	-	ns
t_{BS}	3	-	3	-	3	-	ns	t_{DHC}	2	-	2	-	2	-	ns
t_{BH}	2	-	2	-	2	-	ns	t_{WL}	-	12	-	12	-	12	ns
t_{BMS}	3	-	3	-	3	-	ns	t_{WH}	-	11	-	9	-	7	ns
t_{BMH}	2	-	2	-	2	-	ns	t_{WZ}	-	10	-	10	-	10	ns
t_{WES}	3	-	3	-	3	-	ns	t_{BSADV}	-	0	-	0	-	0	ns
t_{WEH}	2	-	2	-	2	-	ns	$t_{OH(B)}$	2	-	2	-	2	-	ns

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Burst READ followed by Burst WRITE

(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)

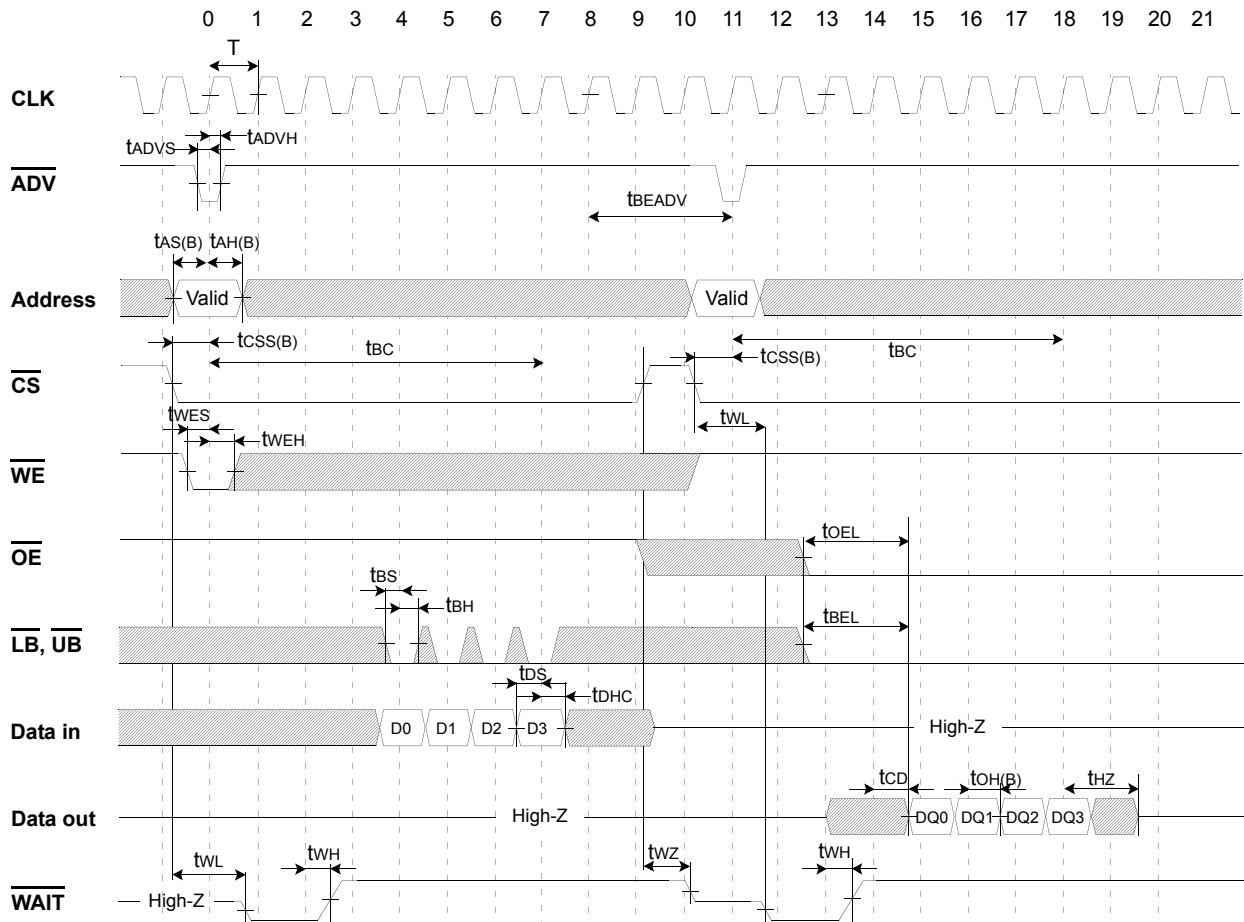


1. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
2. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than tBC(1.7μs)

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Burst WRITE followed by Burst READ

(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



1. Refresh can not be implemented when tBEADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.7us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBEADV.
2. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
 /WAIT High(tWH) : Data available(driven by Latency-1 clock)
 /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than (tBC)1.7μs.